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FAN54300 — USB-Compliant, Dual-Power Input, Single-Cell, Li-Ion Switching Charger with USB-OTG Boost Regulator

Features

- Fully Integrated, High-Efficiency Charger for Single-Cell Li-Ion and Li-Polymer Battery Packs
- Accepts USB or Dedicated Power Input Source
- 5 V, 300 mA Boost Mode for USB OTG from 2.5 to 4.5 V Battery Input
- Charge Voltage Accuracy: ±0.5% at T_A=25°C
 - \pm 1% from T_A=0 to 125°C
- ±5% USB Input Current Regulation Accuracy
- ±5% Charge Current Regulation Accuracy
- 20 V Absolute Maximum Input Voltage
- 9.5 V Maximum Input Operating Voltage on VIN Pin,
 6.5 V Maximum on VBUS Pin
- Up to 1.5 A Maximum Charge Rate
- Programmable Charge and Mode through High-Speed I²C Interface (3.4 Mb/s) with Fast Mode Plus Compatibility
 - Input Current
 - Fast-Charge / Termination Current
 - Charger Voltage
 - Safety Timer
 - Termination Enable
- 3 MHz Synchronous Buck PWM Controller with Wide Duty Cycle Range
- Small Footprint, 1 μH, External Inductors
- Safety Timer with Reset Control
- Weak Input Sources Accommodated by Reducing Charging Current to Maintain Minimum V_{BUS} Voltage
- Low Reverse Leakage from Battery Drain to VBUS or VIN
- Programmable LED Drive for Charge Indication
- Register and Slave Addresses Compatible with FAN540X and FAN542X Families

Description

The FAN54300 combines two highly integrated switch-mode chargers and a boost regulator to minimize single-cell Li-lon charging time from a USB and/or auxiliary power source.

Charging parameters and operating modes are programmable through an I²C Bus® interface that operates up to 3.4 Mbps. The charger and boost regulator circuits switch at 3 MHz to minimize the size of the external passive components.

The FAN54300 provides battery charging in three phases: conditioning, constant current, and constant voltage.

To ensure USB compliance and minimize charging time, the USB input current is limited to the value set through the I^2C host. Charge termination is determined by a programmable minimum current level. A safety timer with reset control provides a safety backup for the I^2C host.

The IC automatically restarts the charge cycle when the battery falls below an internal threshold. If the input source is removed, the IC enters a high-impedance mode, with leakage from the battery to the input prevented. Charge status is reported back to the host through the I²C port. Charge current is reduced when the die temperature reaches 120°C.

The FAN54300 can operate as a boost regulator on command from the system. The boost regulator includes a soft-start that limits inrush current from the battery.

The FAN54300 is available in a 30-bump, 0.4 mm pitch, wafer-level, chip-scale package (WLCSP).

Applications

- Cell Phones, Smart Phones, PDAs
- Digital Cameras
- Portable Media Players

Ordering Information

Part Number	Temperature Range	Package	Packing
FAN54300UCX	-40 to 85°C	30-Ball, WLCSP, 5x6 Array, 0.4mm Pitch, 586 µm Package Height	Tape and Reel

Table 1. Feature Summary

Part Number	Automatic Charge	Battery Absent Charge		
FAN54300	Yes	No		

Typical Application

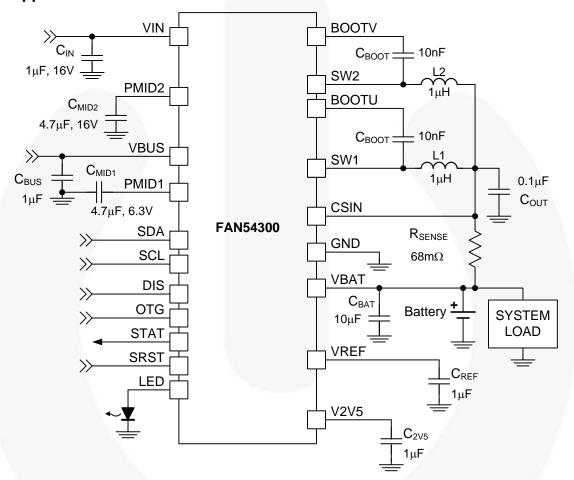


Figure 1. Typical Application

Block Diagrams

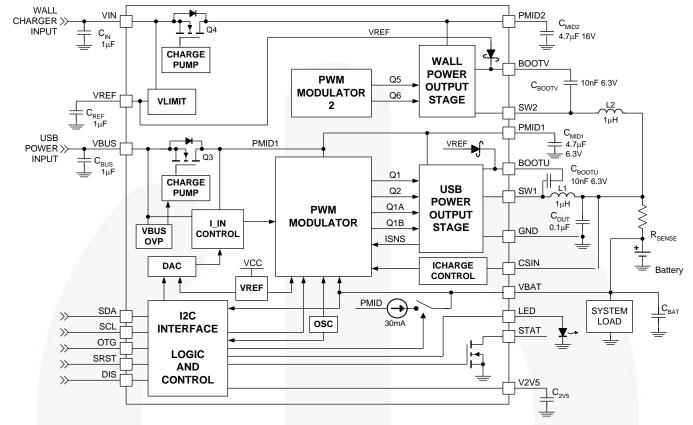


Figure 2. IC and System Block Diagram

Table 2. Recommended External Components

Component	Description	Vendor	Parameter	Тур.	Units
1	Charge Currents to 1 A:	Murata: LQM2MPN1R0M	/ L	1.0	μН
L1, L2:	1 μH, 20%, 1.3 A, 2016	Murata. EQMZMI NTNOM	DCR	85	mΩ
L1, L2.	Charge Currents Above 1 A:	Murata: LQM2HPN1R0M	L	1.0	μН
	1 μH, 20%, 1.6 A, 2520	IVIUIAIA. EQIVIZAFINTROIVI	DCR	55	mΩ
Сват	10 μF, 20%, 6.3 V, X5R, 0603	Murata: GRM188R60J106M	С	10	μF
C _{MID1,2}	4.7 μF, 10%, 16 V, X5R, 0805	Murata: GRM21BR61C475K	С	4.7	μF
C _{IN} , C _{BUS}	1.0 μF, 10%, 16 V, X5R, 0603	Murata GRM188R61E105K	С	1.0	μF
Своот	10 nF, 10%, 6.3 V, X5R, 0201	Murata GRM033R70J103K	С	10	nF
C _{OUT}	0.1 μF, 10%, 6.3 V, X5R, 0201	Murata GRM033R60J104K	С	0.1	μF
C _{2V5} , C _{REF}	1μF, 10%, 6.3 V, X5R, 0402	Murata GRM155R60J105M	С	1.0	μF

Block Diagrams (Continued)

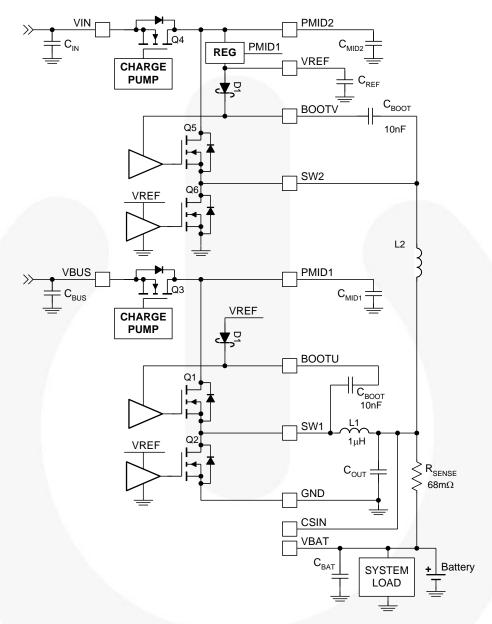


Figure 3. Power Output

Pin Configuration

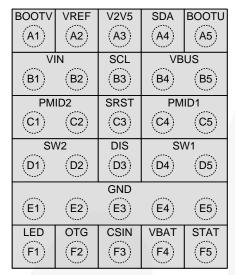


Figure 4. Pin Assignments (Top View)

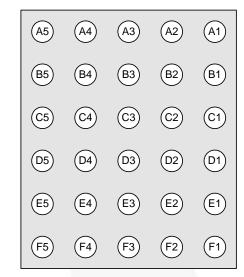


Figure 5. Pin Assignments (Bottom View)

Pin Definitions

Pin#	Name	Description
A1	BOOTV	BOOT. High-side NMOS driver supply. Connect a 10nF capacitor from SW2 to this pin.
A2	VREF	Bias Regulator Output . Connect to a 1 μ F capacitor to PGND. This pin supplies the internal gate drive and power supply to the IC while charging. Up to 5 mA of current can be provided from this pin to drive external circuits. This pin is active when either V_{IN} or V_{BUS} are above V_{BAT} .
А3	V2V5	2.5 V Regulator . Connect to a 1 μ F capacitor to PGND. Up to 5 mA can be provided from this pin to drive external circuits. This regulator is powered only when VIN is connected.
A4	SDA	I ² C Interface Serial Data. This pin should not be left floating.
A5	BOOTU	BOOT. High-side NMOS driver supply. Connect a 10 nF capacitor from SW1 to this pin.
B1, B2	VIN	Charger Input Voltage. Bypass with a minimum of 1 μF, 16 V capacitor to GND.
В3	SCL	I ² C Interface Serial Clock. This pin should not be left floating.
B4, B5	VBUS	USB Input Voltage . Bypass with a 1 μF, 16 V capacitor to GND.
C1, C2	PMID2	Power Input Voltage for VIN Power Source . Power input to the charger regulator, bypass point for the VIN input current sense, and high-voltage input switch. Bypass with a minimum of 4.7 μ F, 16 V capacitor to PGND.
C3	SRST	Safety Reset. When LOW, both safety registers are reset to their default values. When HIGH, the safety registers reset when V _{BAT} drops below V _{SHORT} .
C4, C5	PMID1	Power Input Voltage for VBUS Power Source . Power input to the VBUS switching charger regulator, bypass point for the VBUS input current sense, and high-voltage input switch. Bypass with a minimum of $4.7~\mu\text{F}$, $6.3~\text{V}$ capacitor to PGND.
D1, D2	SW2	Switching Node for VIN Charger. Connect to the output inductor.
D3	DIS	Charge Disable . When this pin is HIGH, charging is disabled and no timers are reset. When LOW, charging is controlled by the I ² C registers. This pin does not affect the 32-second timer.
D4, D5	SW1	Switching Node for VBUS Charger and OTG Boost. Connect to the output inductor.
E1-E5	GND	Ground . Power return for gate drive and power transistors as well as IC signal ground. The connection from this pin to the bottoms of the C _{PMID} capacitors should be as short as possible.
F1	LED	Light Emitting Diode Output . Up to 5 mA current source drive from the active PMID indicates the battery is charging.

Pin #	Name	Description
F2	OTG	On The Go . When unattended charging is indicated, the level on this pin sets the I _{BUS} current limit. This pin is also used to put the IC into Boost Mode.
F3	CSIN	Current-Sense Input . Connect to sense resistor in series with the battery. The IC uses this node to sense current into the battery. Bypass this pin with a 0.1 μF capacitor to PGND.
F4	VBAT	Battery Voltage . Connect to the positive (+) terminal of the battery pack. Bypass with a 10 μF capacitor to PGND.
F5	STAT	Status. Open-drain output indicating charge status. The IC pulls this pin LOW when charging is in process.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol		Parameter	Min.	Max.	Unit
\/	\/DLIQ \/-lt	Continuous	-1.4	.,	
V_{BUS}	VBUS Voltage	Pulsed, 100 ms Maximum Non-Repetitive	-2.0	20.0	V
V _{IN}	VIN Voltage		-2.0	20.0	V
V _{BOOTU}	BOOTU Voltage	OOTU Voltage			
V_{BOOTV}	BOOTV Voltage	OOTV Voltage			
V_{PMID1}	PMID1 Voltage	MID1 Voltage			
V _{SW1}	SW1 Voltage	SW1 Voltage			
V_{PMID2}	PMID2 Voltage	/	-1.0	20.0	V
V _{SW2}	SW2 Voltage		-0.7	12.0	V
Vo	Other Pins		-0.3	6.5 ⁽¹⁾	V
dV _{BUS}	Maximum Rate of V _{BUS} Increas	e Above 5.5 V when IC Enabled		4	V/μs
dV _{IN} dt	Maximum Rate of V _{IN} Increase Above 9.5 V when IC Enabled			4	V/μs
ECD	Electrostatic Discharge	Human Body Model per JESD22-A114	2	2.0	kV
ESD	Protection Level	Charged Device Model per JESD22-C101	1	.5	kV
TJ	Junction Temperature		-40	+150	°C
T _{STG}	Storage Temperature		-65	+150	°C
TL	Lead Soldering Temperature, 1	0 Seconds		+260	°C

Note

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min.	Max.	Units
V_{BUS}	VBUS Supply Voltage	4	6	V
V_{IN}	VIN Supply Voltage	4.0	9.5	V
T _A	Ambient Temperature	-30	+85	°C
TJ	Junction Temperature	0	+125	°C

Thermal Properties

Junction-to-ambient thermal resistance is a function of application and board layout. This data is measured with four-layer 2s2p boards in accordance to JEDEC standard JESD51. Special attention must be paid not to exceed junction temperature $T_{J(max)}$ at a given ambient temperate T_A .

Symbol	Parameter	Typical	Unit
θ_{JA}	Junction-to-Ambient Thermal Resistance	60	°C/W
θ_{JB}	Junction-to-PCB Thermal Resistance	20	°C/W

Lesser of 6.5 V or V_{REF} + 0.3 V.

Electrical Specifications

Unless otherwise specified: circuit of Figure 1, recommended operating temperature range for T_J and T_A , V_{BUS} or $V_{IN} = 5.0 \text{ V}$, HZ1, HZ2, OPA_MODE = 0, (Charger Mode). SCL, SDA, OTG = 0 or 1.8 V. Typical values are for $T_J = 25^{\circ}\text{C}$.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Power Su	ipplies					•
		PWM Switching, Open Battery, TE=0		33		mA
		PWM Not Switching (V _{BAT} > V _{OREG})		3.6		mA
I_{VBUS}	VBUS Current	$0^{\circ}\text{C} < \text{T}_{\text{J}} < 85^{\circ}\text{C}, \text{HZ1} = 1, \text{V}_{\text{BAT}} > \text{V}_{\text{LOWV}}$		350	500	μΑ
		0°C < T _J < 85°C, HZ1 = 1, V _{BAT} < V _{LOWV} , 32S Mode		350	500	μA
		PWM Switching, Open Battery, TE=0		33		mA
		PWM Not Switching (V _{BAT} >V _{OREG})		2.6		mA
I_{VIN}	VIN Current	$0^{\circ}\text{C} < \text{T}_{\text{J}} < 85^{\circ}\text{C}, \text{HZ2} = 1, \text{V}_{\text{IN}} > \text{V}_{\text{LOWV}}$	1	350	500	μΑ
		0°C < T _J < 85°C, HZ2 = 1, V _{IN} < V _{LOWV} , 32S Mode		350	500	μA
	1	0°C < T _J < 85°C, HZ1=HZ2 = 1 or DIS=1, V _{BAT} = 4.2 V			20	μA
I _{BAT}	Battery Discharge Current in High-Z Mode	$0^{\circ}\text{C} < \text{T}_{\text{J}} < 85^{\circ}\text{C}, \text{ V}_{\text{BAT}} = 4.2 \text{ V}, \text{ V}_{\text{IN}} = \text{V}_{\text{BUS}} = \text{Open or GND, HZ1=HZ2=1,} \text{SDA} = \text{SCL} = 1.8 \text{ V}, \text{No I}^2\text{C} \text{ Traffic}$			30	μΑ
Charger \	Voltage Regulation					
	Charge Voltage Range		3.5		4.4	V
V_{OREG}	Charge Voltage Accuracy	T _A = 25°C	-0.5		+0.5	%
		T _J = 0 to 125°C	-1		+1	%
Charging	Current Regulation					
	Output Charge Current Range	$V_{LOWV} < V_{BAT} < V_{OREG},$ $V_{BUS} > V_{SLP}, R_{SENSE} = 68 \text{ m}\Omega$	550		1500	mA
OCHRG	Charge Current Accuracy	20 mV ≤ V _{IREG} ≤ 40 mV	92	97	102	% of Setting
	Across R _{SENSE}	V _{IREG} > 40 mV	94	97	100	
Weak-Bat	ttery Detection		У			•
V_{LOWV}	Weak-Battery Threshold Accuracy	3.4 ≤ V _{LOWV} ≤ 3.7	-5		+5	%
	Weak Battery Deglitch Time	Rising Voltage, 2 mV Overdrive	/	30		ms
Logic Lev	vels: DIS, SDA, SCL, OTG					
V _{IH}	HIGH-Level Input Voltage		1.05			V
V _{IL}	LOW-Level Input Voltage				0.4	V
I _{IN}	Input Bias Current	Input Tied to GND or V _{BAT}		0.01	1.00	μA
Charge T	ermination Detection				UH	
	Termination Current Range	$V_{BAT} > V_{OREG} - V_{RCH}, V_{BUS} > V_{SLP},$ $R_{SENSE} = 68 \text{ m}\Omega$	50		400	mA
I	Tormination Current Assure	[V _{CSIN} – V _{BAT}] from 3 mV to 20 mV	-25%		+25%	
I _(TERM)	Termination Current Accuracy	[V _{CSIN} – V _{BAT}] from 20 mV to 40 mV	-5%		+5%	
	Termination Current Deglitch Time	2 mV Overdrive		30		ms

Electrical Specifications (Continued)

Unless otherwise specified: circuit of Figure 1, recommended operating temperature range for T_J and T_A , V_{BUS} or $V_{IN} = 5.0 \text{ V}$, HZ1, HZ2, OPA_MODE = 0, (Charger Mode). SCL, SDA, OTG = 0 or 1.8V. Typical values are for $T_J = 25^{\circ}\text{C}$.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
VBUS Inp	ut Power Source Detection					•
V _{BUS(MIN)1}	V _{BUS} Input Voltage Rising	To Start V _{BUS} Validation	4.20	4.30	4.40	V
V _{BUS(MIN)2}	Min. V _{BUS} to Pass Validation	During V _{BUS} Validation Period	4.00	4.08	4.15	V
V _{BUS(MIN)3}	Min. V _{BUS} During Charge	During Charging	3.64	3.71	3.78	V
tvbus_valid	V _{BUS} Validation Time			30		ms
VBUS _{LOAD}	V _{BUS} Load	V _{BUS} = 5 V, Applied at V _{BUS} Validation		50		mA
VIN Input	Power Source Detection					•
V _{IN(MIN)1}	V _{IN} Input Voltage Rising	To Start V _{IN} Validation	4.20	4.30	4.40	V
V _{IN(MIN)2}	Min. V _{IN} to Pass Validation	During V _{IN} Validation Period	4.00	4.08	4.15	V
V _{IN(MIN)3}	Min. V _{IN} During Charge	During Charging	3.64	3.71	3.78	V
t _{VBUS_VALID}	V _{IN} Validation Time			30		ms
VIN _{LOAD}	V _{IN} Load	V _{IN} = 5 V, Applied at V _{IN} Validation	N	50		mA
Input Curi	ent Limit					•
. /	VBUS Input Current-Limit	I _{BUS} set to 100 mA	88	93	98	98 500 mA
BUSLIM	Threshold	I _{BUS} set to 500 mA	450	475	500	
V _{2V5} 2.5V I	Linear Regulator					
	2.5 V Regulator Output	I _{2V5} from 0 to 5 mA, V _{IN} > 4.75 V	2.35	2.50	2.65	V
V_{2V5}	Current Limit		6	8		mA
V _{REF} Bias	Generator					
.,	Bias regulator voltage	$V_{IN} > V_{IN(MIN)}$	3.5		6.0	V
V_{REF}	current limit		10	15		mA
Battery Re	echarge Threshold					
.,	Recharge Threshold	Below V _(OREG)	100	120	150	mV
V _{RCH}	Deglitch Time	VBAT falling below V _{RCH} threshold	-//	130		ms
STAT Out	put					ı
V _{STAT(OL)}	STAT Output LOW	I _{STAT} = 10 mA			0.4	V
I _{STAT(OH)}	STAT High Leakage Current	V _{STAT} = 5 V			1	μA
LED Outp	ut			5/2		•
I _{LED(ON)}	LED Output Current Accuracy	V_{LED} from 1.5 to 3.5 V, Max. $(V_{REF}, V_{BAT}) - V_{LED} > 100 \text{ mV}$	-30		+30	%
I _{LED(OFF)}	LED Off-State Leakage Current	V _{LED} = 0 V			1	μA
Battery De	etection			•		
I _{DETECT}	Battery Detection Current Before Charge Complete (Sink Current) ⁽²⁾	Begins After Termination Detected and VBAT ≤ VOREG −VRCH		-0.45		mA
t _{DETECT}	Battery Detection time			262		ms

Electrical Specifications (Continued)

Unless otherwise specified: circuit of Figure 1, recommended operating temperature range for T_J and T_A , V_{BUS} or $V_{IN} = 5.0 \text{ V}$, HZ1, HZ2, OPA_MODE = 0, (Charger Mode). SCL, SDA, OTG = 0 or 1.8 V. Typical values are for $T_J = 25^{\circ}\text{C}$.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Sleep Cor	nparator		1	•	•	
V _{SLP}	Sleep Mode Entry Threshold, V _{BUS} – V _{BAT} or V _{IN} – V _{BAT}	2.3 V ≤ V _{BAT} ≤ V _{OREG} , V _{PWRIN} Falling	0	90	160	mV
	Sleep Mode Exit Hysteresis	$2.3 \text{ V} \leq \text{V}_{BAT} \leq \text{V}_{OREG}$		40		mV
V _{SLP_EXIT}	Deglitch Time for V _{BUS} Rising Above V _{SLP} + V _{SLP_EXIT}	Rising Voltage		30		ms
Power Sw	itches (see Figure 3)					
	Q3 On Resistance (VBUS to PMID1)	IBUS _(LIMIT) ≥ 500 mA		210	300	
	Q1 On Resistance (PMID1 to SW1)			110	225	
D	Q2 On Resistance (SW1 to GND)			130	225	m0
R _{DS(ON)}	Q4 On Resistance (VIN to PMID2)			160	225	mΩ
	Q5 On Resistance (PMID2 to SW2)			110	225	
	Q6 On Resistance (SW2 to GND)			190	350	
Charger F	WM Modulator		1	1		
f _{SW}	Oscillator Frequency		2.7	3.0	3.3	MHz
D _{MAX}	Maximum Duty Cycle				100	%
D _{MIN}	Minimum Duty Cycle			0		%
I _{SYNC}	Synchronous to Non- Synchronous Current Threshold ⁽³⁾	Low-Side MOSFET Cycle-by-Cycle Current Limit		-120		mA
Boost Mo	de Operation (OPA_MODE = 1,	HZ1 = 0)		•		
V	Donat Output Valtage at VDIIC	2.5 V < V _{BAT} < 4.5 V, 0-200 mA Load	4.80	5.05	5.17	\/
V_{BOOST}	Boost Output Voltage at VBUS	2.7 V < V _{BAT} < 4.5 V, 0-300 mA Load	4.77	5.05	5.17	V
BAT(BOOST)	Boost Mode Quiescent Current	PFM Mode, V _{IN} = 3.6 V, I _{OUT} = 0	/	300	400	μА
I _{LIMPK(BST)}	Q2-Peak Current Limit		1160	1380	1550	mA
V _{BAT(MAX)}	Maximum Battery Input for Boost Operation	V _{BAT} Rising	4.7			V
, ,	Hysteresis	V _{BAT} Falling		125		mV
UVLO _{BST}	Minimum Battery Voltage for	While Boost Active		2.42		V
UVLOBST	Boost Operation	To Start Boost Regulator		2.58	2.70	V
VBUS, VII	Load Resistance					
D	VBUS to GND Resistance	Normal Operation	500	1000	1500	Ω
R_{VBUS}	עטט נט טואט אפטוצומוונפ	V _{BUS} Validation	50	110	175	Ω
	VIN to CND Docists	Normal Operation	500	1000	1500	Ω
R_{VIN}	VIN to GND Resistance	V _{IN} Validation	50	110	175	Ω

Electrical Specifications (Continued)

Unless otherwise specified: circuit of Figure 1, recommended operating temperature range for T_J and T_A , V_{BUS} or $V_{IN} = 5.0 \text{ V}$, HZ1, HZ2, OPA_MODE = 0, (Charger Mode). SCL, SDA, OTG = 0 or 1.8 V. Typical values are for $T_J = 25^{\circ}\text{C}$.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Protection	and Timers					
VBUS _{OVP}	VBUS Over-Voltage Shutdown	V _{BUS} Rising	6.12	6.31	6.50	V
VBUSOVP	Hysteresis	V _{BUS} Falling		100		mV
VINI	VIN Over-Voltage Shutdown	V _{IN} Rising	9.5	10.0	10.5	V
VIN _{OVP}	Hysteresis	V _{IN} Falling		100		mV
V	Battery Short-Circuit Threshold	V _{BAT} Rising	2.00	2.05	2.10	V
V_{SHORT}	Hysteresis	V _{BAT} Falling		100		
I _{SHORT}	Short-Circuit Current	V _{BAT} < V _{SHORT}	30	40	50	mA
_	Thermal Shutdown Threshold ⁽⁴⁾	T _J Rising		165		00
T _{SHUTDWN}	Hysteresis ⁽⁴⁾	T _J Falling		10		°C
T _{CF}	Thermal Regulation Threshold (4)	Charge Current Reduction Begins		120		°C
t _{INT}	Detection Interval			2.1		S
t _{32SEC}	32-Second Timer ⁽⁵⁾	32-Second Mode	21.0		31.5	S
t _{15MIN}	15-Minute Timer	15-Minute Mode	12.0	13.5	15.0	min
Δt_{LF}	Low Frequency Timer Accuracy	Charger Inactive	-25		25	%

Notes:

- 2. Refers to negative inductor current. At lower battery charging current, of about 20 mA, non-synchronous switching operation commences.
- 3. Q2 and Q6 always turn on for »60 ns and then turn off if the current is below I_{SYNC}.
- 4. Guaranteed by design.
- 5. This tolerance applies to all timers on the IC, including soft-start and deglitching timers.

I²C Timing Specifications

Guaranteed by design.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Uni
		Standard Mode			100	
	COL Olask Francisco	Fast Mode			400	
f _{SCL}	SCL Clock Frequency	High-Speed Mode, C _B ≤ 100 pF			3400	kHz
		High-Speed Mode, C _B ≤ 400 pF			1700	
	Bus-Free Time between STOP	Standard Mode		4.7		
t _{BUF}	and START Conditions	Fast Mode		1.3		μS
		Standard Mode		4		μS
t _{HD;STA}	START or Repeated START Hold Time	Fast Mode		600		ns
	Tiola Time	High-Speed Mode		160		ns
	// \	Standard Mode		4.7		μ
		Fast Mode		1.3		μ
t_{LOW}	SCL LOW Period	High-Speed Mode, C _B ≤ 100 pF		160		ns
	7.	High-Speed Mode, C _B ≤ 400 pF		320		ns
	1	Standard Mode		4		μ
- 4	SCL HIGH Period	Fast Mode		600		n:
t _{HIGH}		High-Speed Mode, C _B ≤ 100 pF		60		n
		High-Speed Mode, C _B ≤ 400 pF		120		n
	Repeated START Setup Time	Standard Mode		4.7		μ
t _{SU;STA}		Fast Mode		600		n
		High-Speed Mode		160		n
		Standard Mode		250		
t _{SU;DAT}	Data Setup Time	Fast Mode		100		n
	A	High-Speed Mode	/	10		
		Standard Mode	0		3.45	μ
		Fast Mode	0		900	n
t _{HD;DAT}	Data Hold Time	High-Speed Mode, C _B ≤ 100 pF	0		70	n
		High-Speed Mode, C _B ≤ 400 pF	0		150	n
		Standard Mode	20+0).1C _B	1000	
	001 5: -	Fast Mode	20+0).1C _B	300	
t _{RCL}	SCL Rise Time	High-Speed Mode, C _B ≤ 100 pF		10	80	n
		High-Speed Mode, C _B ≤ 400 pF		20	160	
		Standard Mode	20+0).1C _B	300	٦
	001 5 11 7	Fast Mode		20+0.1C _B		
t _{FCL}	SCL Fall Time	High-Speed Mode, C _B ≤ 100 pF		10	40	n
		High-Speed Mode, C _B ≤ 400 pF		20	80	
	ODA Die a Tiera	Standard Mode	20+0	20+0.1C _B		
t_{RDA}	SDA Rise Time Rise Time of SCL after a	Fast Mode	20+0).1C _B	300	
t _{RCL1}	Repeated START Condition	High-Speed Mode, C _B ≤ 100 pF		10	80	ns
	and after ACK Bit	High-Speed Mode, C _B ≤ 400 pF		20	160	

I²C Timing Specifications

Guaranteed by design.

Symbol	Parameter	Conditions		Тур.	Max.	Unit
t _{FDA}		Standard Mode	20+0.1C _B		300	
	SDA Fall Time	Fast Mode	20+0.1C _B		300	20
		High-Speed Mode, C _B ≤ 100 pF		10	80	ns
		High-Speed Mode, C _B ≤ 400 pF		20	160	
	Stop Condition Setup Time	Standard Mode		4		μS
t _{SU;STO}		Fast Mode		600		ns
		High-Speed Mode		160		ns
Св	Capacitive Load for SDA, SCL				400	pF

Timing Diagrams

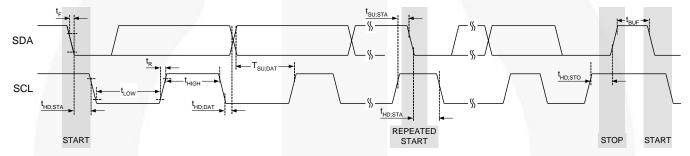


Figure 6. I²C Interface Timing for Fast and Slow Modes

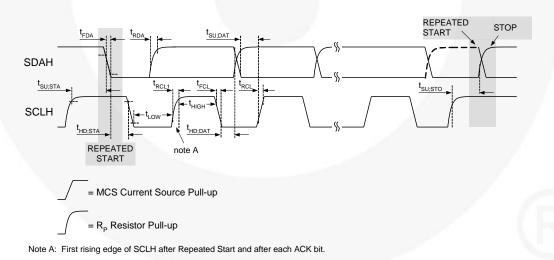
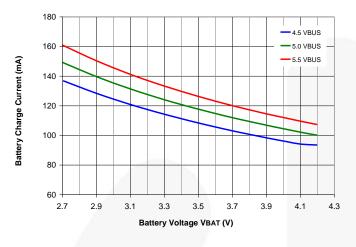


Figure 7. I²C Interface Timing for High-Speed Mode

VBUS Charge Mode Typical Characteristics

Unless otherwise specified, circuit of Figure 1, V_{OREG}=4.2 V, V_{BUS}=5.0 V, and T_A=25°C.



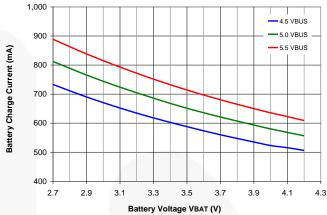
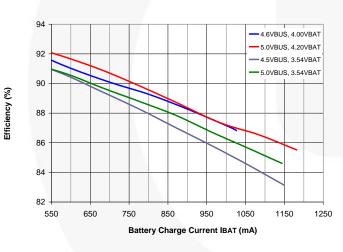


Figure 8. Battery Charge Current vs. V_{BUS} with $I_{\text{INLIM}} = 100 \text{ mA}$

Figure 9. Battery Charge Current vs. V_{BUS} with I_{INLIM} =500 mA



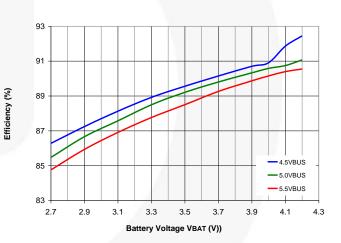


Figure 10. Charger Efficiency, No I_{INLIM}, I_{OCHARGE}=1250 mA

Figure 11. Charger Efficiency vs. V_{BUS} , I_{INLIM} =500 mA

VBUS Charge Mode Typical Characteristics

Unless otherwise specified, circuit of Figure 1, V_{OREG}=4.2 V, V_{BUS}=5.0 V, and T_A=25°C.

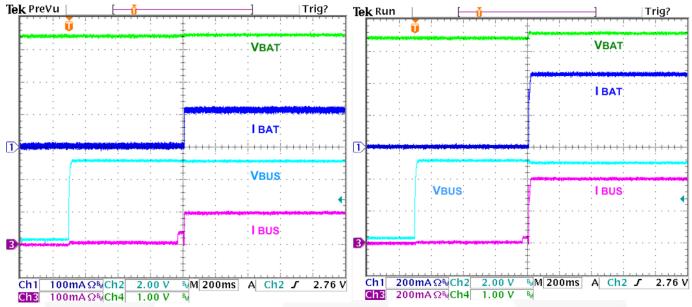


Figure 12. Auto-Charge Startup at V_{BUS} Plug-in, I_{INLIM} =100 mA, OTG=1, V_{BAT} =3.4 V

Figure 13. Auto-Charge Startup at V_{BUS} Plug-in, I_{INLIM} =500 mA, OTG=1, V_{BAT} =3.4 V

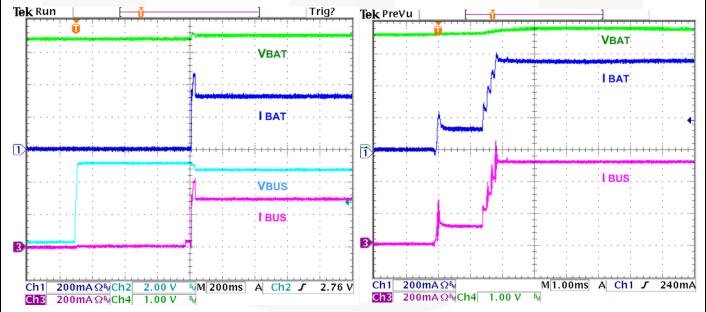


Figure 14. AutoCharge Startup with 300 mA Limited Charger / Adaptor, $I_{\rm INLIM}$ =500 mA, OTG=1, $V_{\rm BAT}$ =3.4 V

Figure 15. Charger Startup with HZ_MODE Bit Reset, $I_{\text{INLIM}}\!\!=\!\!500$ mA, $I_{\text{OCHARGE}}\!\!=\!\!950$ mA, $V_{\text{OREG}}\!\!=\!\!4.2$ V, $V_{\text{BAT}}\!\!=\!\!3.6$ V

VBUS Charge Mode Typical Characteristics

Unless otherwise specified, circuit of Figure 1, V_{OREG}=4.2 V, V_{BUS}=5.0 V, and T_A=25°C.

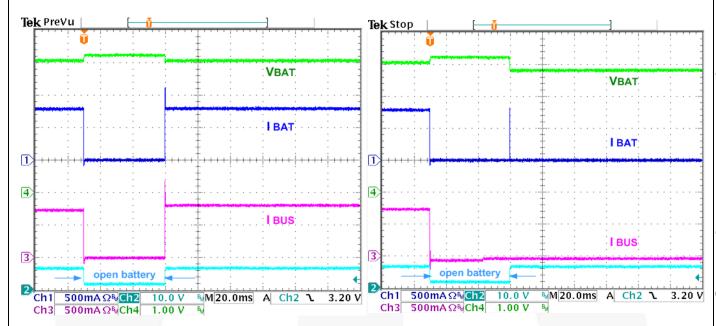


Figure 16. Battery Removal / Insertion during Charging, $V_{\text{BAT}} \! = \! 3.9 \text{ V}, I_{\text{OCHARGE}} \! = \! 950 \text{ mA}, \text{No } I_{\text{INLIM}}, \text{TE=0}$

Figure 17. Battery Removal / Insertion during Charging, V_{BAT} =3.9 V, $I_{OCHARGE}$ =950 mA, No I_{INLIM} , TE=1

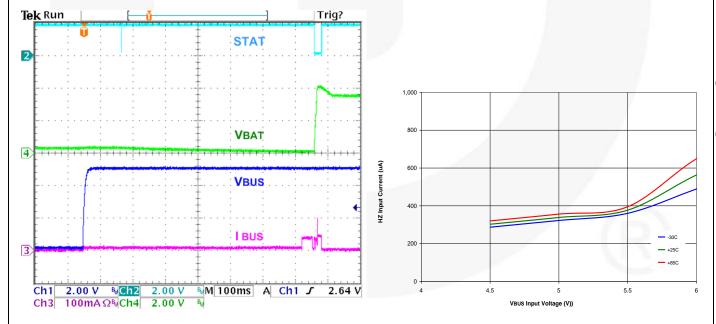
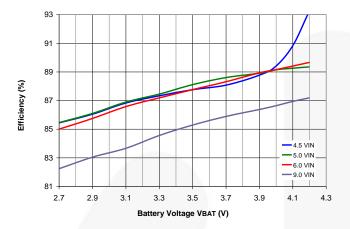


Figure 18. No Battery at V_{BUS} Power-up

Figure 19. VBUS Current in High-Impedance Mode with Battery Open

VIN Charger Characteristics

Unless otherwise specified, circuit of Figure 1, $V_{OREG} = 4.2 \text{ V}$, $V_{IN} = 5.0 \text{ V}$, and $T_A = 25 ^{\circ}\text{C}$.



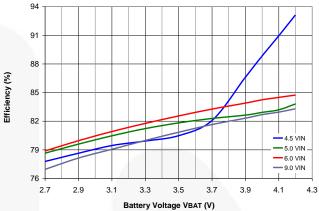
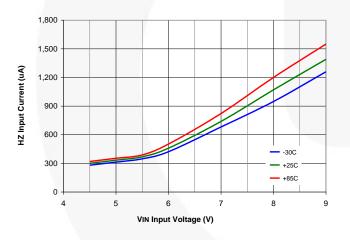


Figure 20. Charger Efficiency, I_{OCHARGE}=950 mA

Figure 21. Charger Efficiency, I_{OCHARGE}=1550 mA



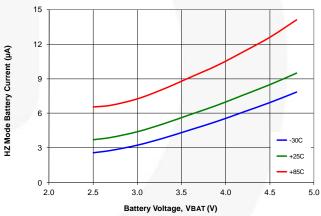


Figure 22. V_{IN} Current in High-Impedance Mode, V_{BAT}=3.6 V

Figure 23. Battery Current in High-Impedance Mode, VBUS=Open, V_{IN}=Open

VIN Charger Characteristics

Unless otherwise specified, circuit of Figure 1, $V_{OREG} = 4.2 \text{ V}$, $V_{IN} = 5.0 \text{ V}$, and $T_A = 25 ^{\circ}\text{C}$.

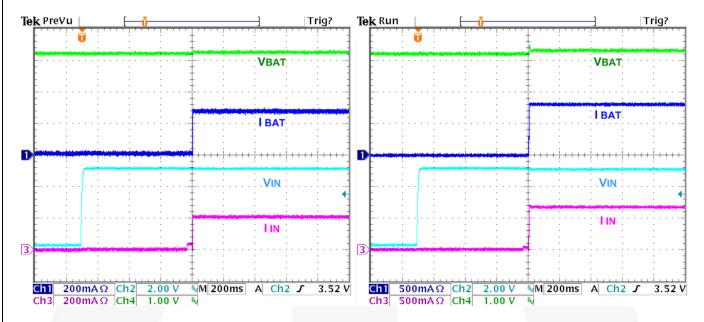


Figure 24. Auto-Charge Startup at V_{IN} Plug-in, V_{BAT} =3.2 V, IO_LEVELV = 1

Figure 25. Auto-Charge Startup at V_{IN} Plug-in, V_{BAT} =3.2 V, $I_{OCHARGE}$ =950 mA

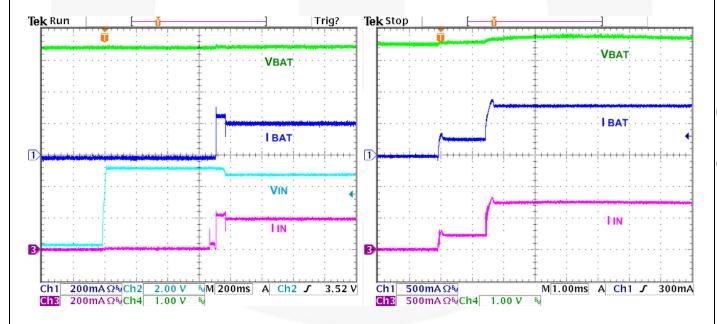


Figure 26. Auto-Charge Startup with 200 mA Limited Charger / Adaptor, V_{BAT} =3.4 V

Figure 27. Charger Startup with HZ_MODE Bit Reset, I_{OCHARGE}=950 mA, V_{OREG}=4.2 V, V_{BAT}=3.6 V

VIN Charger Characteristics

Unless otherwise specified, circuit of Figure 1, $V_{OREG} = 4.2 \text{ V}$, $V_{IN} = 5.0 \text{ V}$, and $T_A = 25 ^{\circ}\text{C}$.

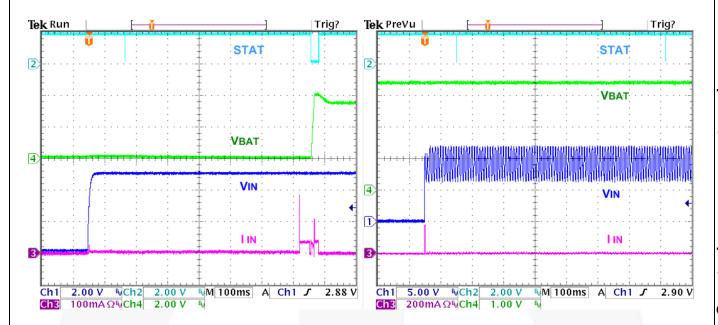


Figure 28. No Battery at VIN Power-up

Figure 29. Non-Compliant Charger Rejection, V_{BAT} =3.4 V

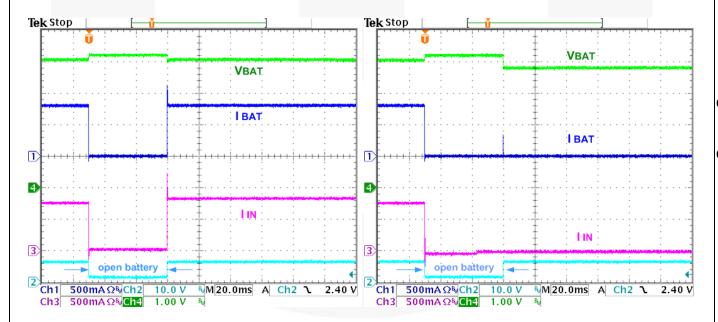


Figure 30. Battery Removal / Insertion During Charging, V_{BAT} =3.9 V, $I_{OCHARGE}$ =950 mA, TE=0

Figure 31. Battery Removal / Insertion During Charging, V_{BAT} =3.9 V, $I_{OCHARGE}$ =950 mA, TE=1

Boost Mode Typical Characteristics Unless otherwise specified, using the circuit of Figure 1, V_{BAT}=3.6 V, T_A=25°C. 100 100 95 90 Efficiency (%) Efficiency (%) 85 85 80 80 75 75 3.6VBAT 4.2VBAT 70 70 50 200 300 0 100 150 250 0 VBUS Load Current (mA) Figure 32. Efficiency vs. VBAT

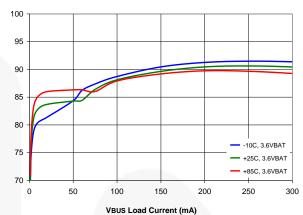
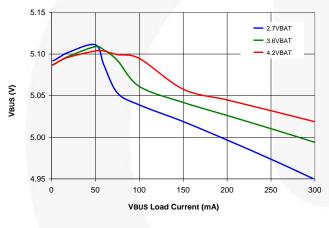


Figure 33. Efficiency Over Temperature



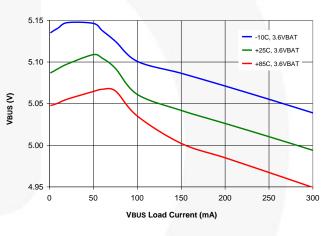
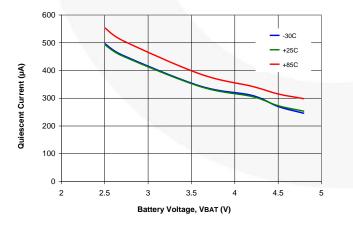


Figure 34. Output Regulation vs. VBAT

Figure 35. Output Regulation Over Temperature



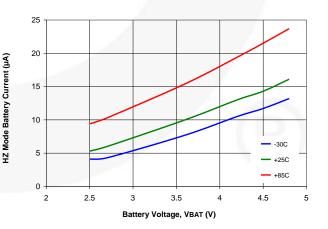


Figure 36. Quiescent Current

Figure 37. High-Impedance Mode Battery Current

Boost Mode Typical Characteristics

Unless otherwise specified, using the circuit of Figure 1, V_{BAT}=3.6 V, T_A=25°C.

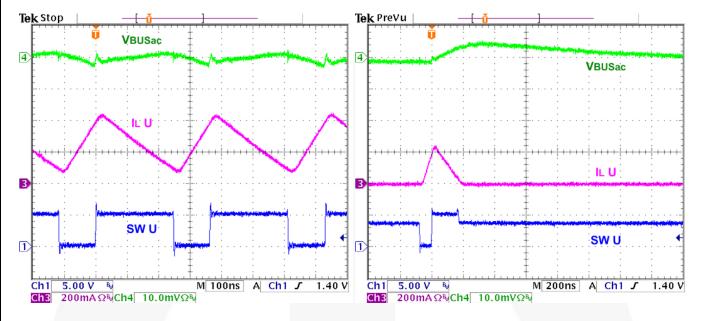


Figure 38. Boost PWM Waveform

Figure 39. Boost PFM Waveform

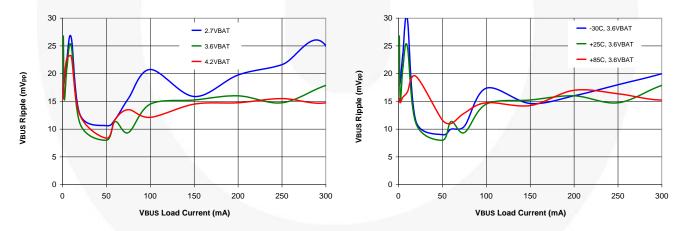


Figure 40. Output Ripple vs. VBAT

Figure 41. Output Ripple vs. Temperature

Boost Mode Typical Characteristics

Unless otherwise specified, using the circuit of Figure 1, V_{BAT}=3.6 V, T_A=25°C.

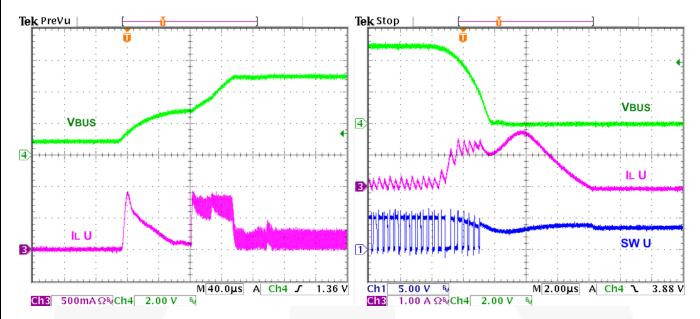


Figure 42. Startup, 3.6 V_{BAT} , 50 Ω Load, Additional 10 μF , X5R Across VBUS

Figure 43. V_{BUS} Fault Response, 3.6 V_{BAT}

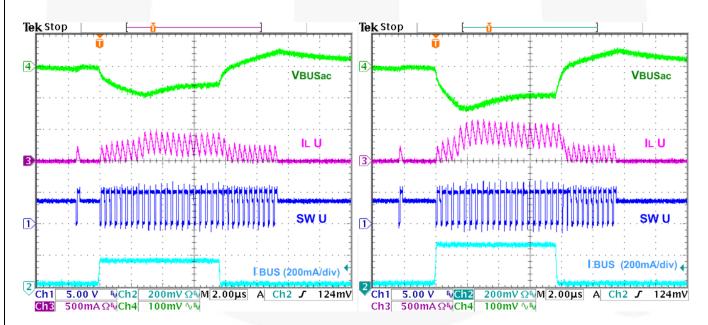


Figure 44. Load Transient, 5-155-5 mA, t_R=t_F=100 ns

Figure 45. Load Transient, 5-255-5 mA, t_R = t_F =100 ns

Circuit Description / Overview

When charging batteries with a current-limited input source, such as USB, a switching charger's high efficiency over a wide range of output voltages minimizes charging time.

The FAN54300 combines two highly integrated synchronous buck regulators for charging from two separate power sources. The IC also includes a synchronous boost regulator, which can supply 5 V to USB On-The-Go (OTG) peripherals. The regulator employs synchronous rectification for both the charger and boost regulators to maintain high efficiency over a wide range of battery voltages and charge states.

In addition to its USB (VBUS) input, the FAN54300 allows a second power source (VIN) to be used for charging. This input source is typically a "wall wart" and can be up to 9.5 V input.

The FAN54300 has three operating modes:

Charge Mode:

Charges a single-cell Li-lon or Li-polymer battery.

Boost Mode

Provides 5 V power to USB-OTG with an integrated synchronous rectification boost regulator using the battery as input.

High-Impedance Mode:

Both the boost and charging circuits are off in this mode. Current flow from PWRIN (the charging power source) to the battery, or from the battery to PWRIN, are blocked in this mode. This mode consumes very little current from PWRIN or the battery.

When the IC is charging the battery from VIN, the boost regulator may be simultaneously enabled to supply 5 V for OTG peripherals.

Charge Mode

In Charge Mode, FAN54300 employs five regulation loops:

- VBUS input current: Limits the amount of current drawn from VBUS. This current is sensed internally and can be programmed through the I²C interface
- Charging current: Limits the maximum charging current. This current is sensed using an external R_{SENSE} resistor.
- 3. Charge voltage: The regulator is restricted from exceeding this voltage. As the internal battery voltage rises, the battery's internal impedance and R_{SENSE} works in conjunction with the charge voltage regulation to decrease the amount of current flowing to the battery. Battery charging is completed when the voltage across R_{SENSE} drops below the I_{TERM} threshold.
- Temperature: If the IC's junction temperature reaches 120°C, charge current is continuously reduced until the IC's temperature stabilizes at 120°C.
- An additional loop limits the amount of drop on VBUS or VIN to a programmable voltage (V_{SP}) to accommodate current-limited wall chargers.

Input Source Selection

The FAN54300 selects the power source (PWRIN) for charging according to the following criteria.

Table 3. PWRIN: Charging Power Input Source Selection

V _{IN}	V _{BUS}	PWRIN
VALID	INVALID	V _{IN}
INVALID	VALID	V_{BUS}
VALID	VALID	V _{IN}

If charging is in progress with V_{BUS} and V_{IN} becomes valid, charging from VBUS stops and charging continues from V_{IN} . Charging stops if HZ_VIN is set when V_{IN} becomes valid while charging with V_{BUS} .

If VIN and VBUS are both connected and t_{15MIN} expires, both CE# bits are set. To reinitiate t_{15MIN} charging (autocharge) with a weak battery, both power sources must be unplugged, then a valid power source plugged in. If only one of the two connected sources are removed then connected with a weak battery, both CE# bits remain set.

Fault Reporting and Register Reset

All faults that occur during charging or boost are reported only in the STATUS register (R0) associated with the active charging source at the time of the fault. Any register reset that occurs due to t_{32SEC} overflow resets only the registers associated with the active charging source.

For example: Assume the IC is charging in 32-Second Mode with V_{IN} as a source. The processor stops setting TMR_RST, so $t_{32\text{SEC}}$ expires. The IC then resets only the _V registers and goes into 15-Minute Mode charging with V_{IN} . A timer fault is enunciated, but reported in the CONTROLO_V register. CONTROLO_U is unaffected by this event. When the $t_{15\text{MIN}}$ timer expires, the IC sets the CE#_V bit, but leaves the CE#_U bit unchanged.

Battery Charging Curve

If the battery voltage is below V_{SHORT} , a linear current source "pre-charges" the battery until V_{BAT} reaches V_{SHORT} . The PWM charging circuits are then started and the battery is charged with a constant current if sufficient input power is available. The current slew rate is limited to prevent overshoot.

The FAN54300 is designed to work with a current-limited input source at PWRIN. During the current regulation phase of charging, PWRIN current limitations or the programmed charging current limit the amount of current available to charge the battery and power the system. The effect of input power limitations on I_{CHARGE} can be seen in Figure 47.

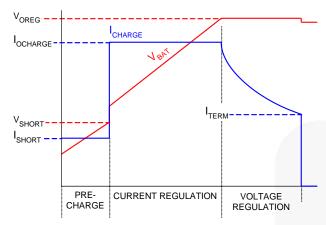


Figure 46. Charge Curve when PWRIN Limitations Don't Limit I_{CHARGE}

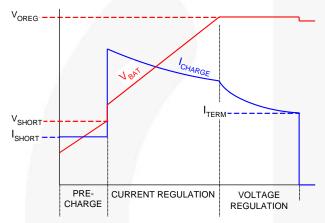


Figure 47. Charge Curve when PWRIN Limits I_{CHARGE}

PWRIN limitations are controlled either by:

- IBUSLIM: These bits set the maximum amount of current that the charger draws from VBUS; OR
- SP_CHARGER: For power-limited chargers, the FAN54300 limits current draw when the charging source drops to the voltage programmed by the SP_CHARGER bits. This allows "travel adapters" to be accommodated without host software overhead. The SP_CHARGER control loop applies to both VIN and VBUS.

Assuming V_{OREG} is programmed to the cell's fully charged "float" voltage, the current the battery accepts with the PWM regulator limiting its output (sensed at VBAT) to VOREG declines and the charger enters the voltage regulation phase of charging. When the current declines to the programmed I_{TERM} value, the charge cycle is complete. Charge current termination can be disabled by resetting the TE bit.

Charger Programmability

Throughout this document, any parameter that ends in "U" applies when charging from V_{BUS} and any parameter ending in "V" applies when charging from V_{IN} . Parameters set with slave address D6 are applied when charging from V_{BUS} . Parameters set with slave address D4 are applied when charging from V_{IN} .

The following charging and input power control parameters can be programmed by the host through I²C.

Table 4. Programmable Charging Parameters

Parameter	Charging Source	Name	Register
Output Voltage Regulation	Either	OREG	REG2[7:2]
Battery Charging	V_{BUS}	ICHGU	REG4[6:4]
Current Limit	V _{IN}	ICHGV	REG4[6:3]
Input Current Limit	V _{BUS}	IBUSLIM	REG1[7:6]
Charge Termination Limit	Either	ITERM	REG4[2:0]
Special Charger Minimum Voltage	Either	VSP	REG5[2:0]

The charger output or "float" voltage can be programmed by the OREG bits from 3.5 V to 4.44 V in 20 mV increments.

Table 5. OREG Bits (REG2 [7:2]) vs. Charger V_{OUT} (V_{OREG}) Float Voltage

(V _{OREG}) Float Voltage											
Decimal	Hex	VOREG	Decimal	Hex	VOREG						
0	00	3.50	32	20	4.14						
1	01	3.52	33	21	4.16						
2	02	3.54	34	22	4.18						
3	03	3.56	35	23	4.20						
4	04	3.58	36	24	4.22						
5	05	3.60	37	25	4.24						
6	06	3.62	38	26	4.26						
7	07	3.64	39	27	4.28						
8	08	3.66	40	28	4.30						
9	09	3.68	41	29	4.32						
10	0A	3.70	42	2A	4.34						
11	0B	3.72	43	2B	4.36						
12	0C	3.74	44	2C	4.38						
13	0D	3.76	45	2D	4.40						
14	0E	3.78	46	2E	4.42						
15	0F	3.80	47	2F	4.44						
16	10	3.82	48	30	4.44						
17	11	3.84	49	31	4.44						
18	12	3.86	50	32	4.44						
19	13	3.88	51	33	4.44						
20	14	3.90	52	34	4.44						
21	15	3.92	53	35	4.44						
22	16	3.94	54	36	4.44						
23	17	3.96	55	37	4.44						
24	18	3.98	56	38	4.44						
25	19	4.00	57	39	4.44						
26	1A	4.02	58	ЗА	4.44						
27	1B	4.04	59	3B	4.44						
28	1C	4.06	60	3C	4.44						
29	1D	4.08	61	3D	4.44						
30	1E	4.10	62	3E	4.44						
31	1F	4.12	63	3F	4.44						

Note:

6. All register default settings are noted by **bold typeface**.

Charge Initiation

A new charge cycle begins when one of the following occurs:

- The battery voltage falls below V_{OREG} V_{RCH}
- A power source is connected (PWRIN POR) and battery voltage is below the weak-battery threshold (V_{LOWV}).
- CE# and HZ_MODE are both cleared, after having been set, and a power source is connected.

Charge Current Limit

The default charge current is limited by the IOLEVEL bit (REG5[5]). When this bit is set (default), charge current is limited to 325 mA (22.1 mV across R_{SENSE}) and the ICHG bits are ignored. Resetting IOLEVEL allows the ICHG bits to control the battery charge current limit.

Any attempt to write a value higher than 10 (0AH) results in a value of 10 (0AH) written to the ICHGV bits (see Table 24).

Charge Termination Current Limit

Current charge termination is enabled when TE (REG1[3]) = 1. The current level is control by the ITERM bits (REG4[2:0].

PWM Controller in Charge Mode

The IC uses a current-mode PWM controller to regulate the output voltage and battery charge currents. A cycle-by-cycle current limit of nominally 2.3 A, sensed through Q1, is used to terminate t_{ON} . The synchronous rectifier, Q2, also has a current limit that turns off Q2 at 160mA to prevent current flow from the battery.

When the charge current drops below ~20 mA; the IC runs in Asynchronous Mode, which prevents reverse current from pumping up the input source.

Safety Timer (see Figure 52)

At the beginning of the charging process, the IC starts the 15-minute timer ($t_{15\text{MIN}}$). When this timer expires, charging is terminated and the CE# bit is set. Writing to any register through I²C stops the $t_{15\text{MIN}}$ timer, which, in turn, starts a 32-second timer ($t_{32\text{SEC}}$). Setting the TMR_RST bit (REG0[1]) resets the $t_{32\text{SEC}}$ timer. If the $t_{32\text{SEC}}$ timer times out, all registers (except SAFETY) are set to their default values, a Timer Fault (110) is reported in the fault register, and charging resumes using the default values with the $t_{15\text{MIN}}$ timer running.

Since there is only one t_{32SEC} timer on the IC, writing to either TMR_RST bit in either CONTROL0_U or CONTROL0_V resets the timer. The t_{32SEC} timer starts with an I 2 C WRITE to either slave address. Timer faults are reported in both U and V registers. A t_{32SEC} fault resets U and V registers 1 – 5.

Normally, charging is controlled by the host with the t_{32SEC} timer running to ensure that the host is active. Charging with the t_{15MIN} timer running is used for charging that is unattended by the host, which would occur when V_{BAT} is insufficient to power the host processor. If the 15-minute timer expires, the IC turns off the charger and indicates a timer fault (110) on the FAULT bits (REG0[2:0]). This prevents overcharge if the host fails to reset the t_{32SEC} timer. The CE# bit is set in the registers where the power sources are connected. For example, if VIN and VBUS are both connected when the t_{15MIN} timer expires, CE#_V and CE_U are both set.

Reset Bit

Setting the RESET bit (Reg4[7]) resets all registers for the slave address used to set the RESET bit. When the RESET bit is set, the $t_{\rm 32SEC}$ timer is reset and stopped, charging stops and the IC goes to Charge Configuration Mode (see Figure 50). If $V_{\rm BAT}$ < $V_{\rm OREG}$, charging begins in 15-Minute Mode 262 ms after the RESET bit is set.

PWRIN Validation, Notification, and Non-Compliant Power Source Rejection

Whenever either VBUS_CON or VIN_CON bits have been set, the STAT pin pulses to notify the host processor of a change in status on the input power supply.

Before attempting to charge, the IC attempts to validate its input source by loading the appropriate source with 110 Ω to ensure that the source stays between 4.4 V and VIN $_{\text{OVP}}$ for 32 ms. If the input source fails validation, STAT enunciates a fault and the fault bits are set according to the condition of the input source (OVP or poor input source). The PWRIN validation sequence always occurs before charging is initiated or re-initiated (for example, after a PWRIN OVP fault, a V_{RCH} recharge initiation, or resetting the HZ bit). The 32 ms validation time ensures that unfiltered 50/60 Hz chargers and other non-compliant chargers are rejected.

2.5 V Regulator Operation

When the VIN_CON bit is set, indicating that the VIN power source has been plugged in, the V2V5 regulator is enabled.

USB-Friendly Boot Sequence (see Figure 48)

At PWRIN POR, when the battery voltage is above the weak-battery threshold (V_{LOW}), the IC goes into Charge Configuration Mode unless the t_{32SEC} timer is enabled by an I²C write. In that case, the IC begins to charge with the existing register settings.

If $V_{BAT} < V_{LOW}$, the IC goes into Charge Configuration Mode if the t_{32SEC} timer is not enabled. If $V_{BAT} < V_{OREG}$, the registers reset and charging begins in 15-Minute Mode. During 15-Minute Mode, the charger uses an input current limit controlled by the OTG pin when charging from VBUS (100mA if OTG is LOW and 500mA if OTG is HIGH).

Even if charging from VIN, the charging current is limited to 325 mA (22.14 mV across $68m\Omega$) after the registers are reset. This feature can revive a cell whose voltage is too low for reliable host operation until the battery has sufficient charge for the host to boot up and set charge parameters. Charging continues in the absence of host communication even after the battery has reached V_{OREG}, with a default value of 3.54 V, and the charger remains active until t_{15MIN} times out.

Once the host processor begins writing to the IC, charging parameters are set by the host, which must continually reset the t_{32SEC} timer to continue charging using programmed charging parameters. If t_{32SEC} times out, the register defaults are loaded, the FAULT bits are set to 110, STAT is pulsed, and charging continues with default charge parameters.

At PWRIN POR, if $V_{BAT} < V_{LOW}$ and HZ or CE# were set previously, the IC goes into HZ state, which causes the registers to reset, clearing the HZ and CE# bits when t_{32SEC} expires and beginning t_{15MIN} charging unless the host processor sets the TMR_RST bit.

VBUS Current Limiting

To minimize charging time without overloading VBUS's current limitations, the IC's VBUS current limit can be programmed with the IBUSLIM bits (REG1[7:6]).

The OTG pin establishes the VBUS current limit during 15-Minute Mode charging.

Operational Flow Charts

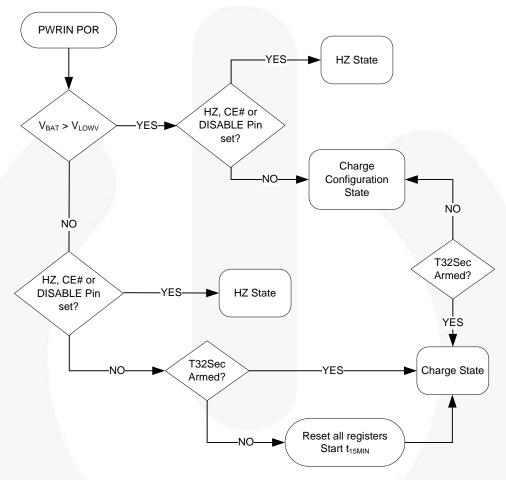
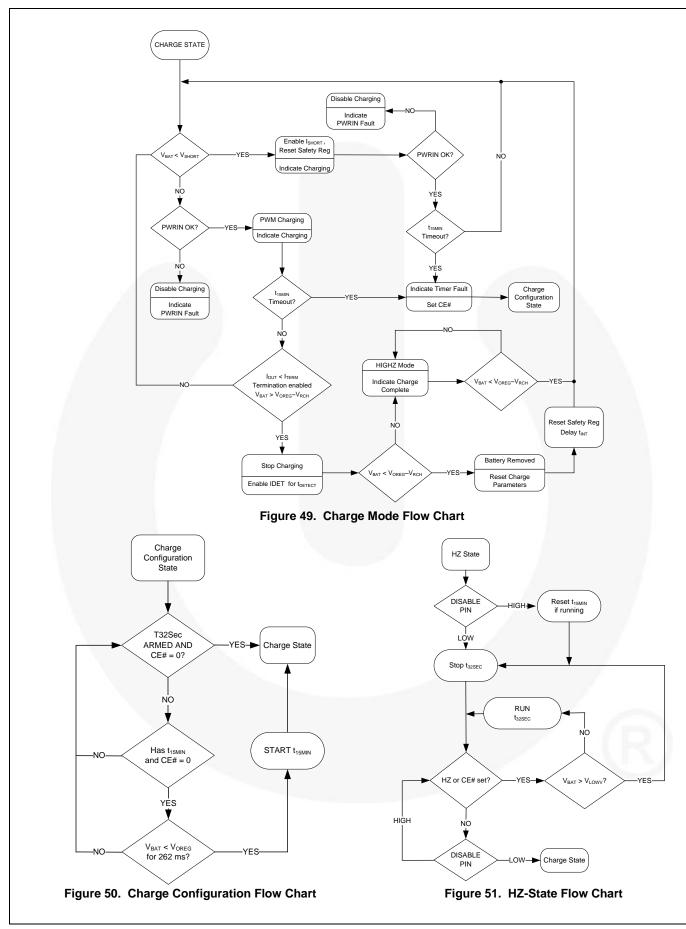


Figure 48. Charger PWRIN POR Flow Chart



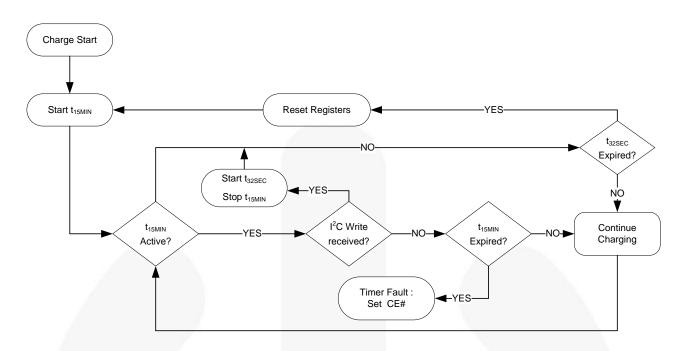


Figure 52. Timer Flow Chart

Special Charger

The IC limits input current in case a current-limited charger is supplying V_{BUS} or V_{IN} . The IC slowly increases the charging current until either:

- I_{BUSLIM} or I_{CHARGE} is reached; or
- V_{PWRIN} = V_{SP} where V_{PWRIN} is the selected input power source (see Table 4).

If V_{PWRIN} collapses to V_{SP} when current is ramping up, the IC charges with an input current that keeps $V_{PWRIN} = V_{SP}$. When the V_{SP} control loop is limiting the charge current, the SP bit (REG5[4]) is set. V_{SP} default value is 4.53 V, but it can be programmed by REG5[2:0].

Safety Settings

A SAFETY register (REG6) prevents the values in OREG (REG2[7:2]) and ICHG (REG4[6:3]) from exceeding the values of the VSAFE and ISAFE values.

After V_{BAT} rises above V_{SHORT} , the SAFETY register is loaded with its default value and may be written only before any other register is written. After writing to any other register, the SAFETY register is locked until V_{BAT} falls below V_{SHORT} . The SAFETY register is reset whenever the SRST pin is LOW.

ISAFE and VSAFE establish values that limit the maximum values of ICHG and OREG used by the control logic. If the host attempts to write a value higher than VSAFE or ISAFE to OREG or ICHG, respectively; the VSAFE, ISAFE value appears as the OREG, ICHG register value, respectively.

For the SAFETY_U register, any attempt to write an ISAFE value higher than 10 (0AH) results in a value of 10 being written to the ISAFE bits. See Table 21 for VSAFE values and Table 20 and Table 26 for ISAFE values.

Thermal Regulation and Protection

When the IC's junction temperature reaches T_{CF} (about 120°C) the charger reduces its output current to prevent overheating. If the temperature continues to increase, the current is reduced to 0 when the junction is 10°C above T_{CF} . If the temperature increases beyond $T_{SHUTDOWN}$, charging is suspended, the FAULT bits are set to 101, and SAT is pulsed. In Suspend Mode, all timers stop and the state of the IC's logic is preserved. Charging resumes after the die cools to about 10°C below $T_{SHUTDOWN}$.

Charge Mode Input Supply Protection Sleep Mode

When V_{BUS} and V_{IN} are both below V_{BAT} , the IC enters Sleep Mode. To prevent the battery from discharging into VBUS, reverse current is prevented by body switching Q1 when PMID1 falls below V_{BAT} .

Similarly, when V_{IN} falls below $V_{\text{BAT}},\ Q4$ turns off, blocking battery current flow into VIN.

Input Supply Low-Voltage Detection

The IC continuously monitors V_{PWRIN} during charging. If the input voltage for the active charging source falls below 3.7 V, the IC terminates charging, pulses the STAT pin, sets STAT bits to 11, and sets the FAULT bits to 011 for the appropriate input source.

If the power source recovers above the $V_{\text{IN(MIN)}}$ rising threshold after timer t_{INT} (about two seconds), the charging process is repeated. This prevents the USB power bus from collapsing or oscillating when the IC is connected to a suspended USB port or an OTG device with low current capability.

Input Over-Voltage Detection

When V_{BUS} exceeds its OVP threshold, the IC:

- 1. Turns off Q3:
- 2. Suspends charging from V_{BUS}; and
- Sets the FAULTU bits to 001, STATU bits to 11, and pulses the STAT pin.

When V_{BUS} falls to about 150 mV below VBUS_{OVP}, the fault is cleared, and charging resumes after V_{BUS} is revalidated.

If V_{IN} exceeds its OVP threshold, the IC:

- 1. Turns off Q4;
- 2. Suspends charging from V_{IN}; and
- Sets the FAULTV bits to 001, STATV bits to 11, and pulses the STAT pin.

Charge Mode Battery Detection & Protection

VBAT Over-Voltage Protection

The OREG voltage regulation loop prevents V_{BAT} from overshooting the OREG voltage by more than 50 mV when the battery is removed. When the PWM charger is running with no battery, the TE bit is not set, and a battery is inserted that's charged to a voltage higher than V_{OREG} ; PWM pulses stop. If no further pulses occur for 30 ms, the IC sets the FAULT bits to 100, STAT bits to 11, and pulses the STAT pin.

Battery Detection During Charging

The IC can detect presence, absence, or removal of a battery. During normal charging, once V_{BAT} is greater than $V_{\text{OREG}}-V_{\text{RCH}}$ and the termination charge current is detected; the IC terminates charging and sets the STAT bits to 10. It then turns on a discharge current, I_{DETECT} , for t_{DETECT} . If V_{BAT} is still above $V_{\text{OREG}}-V_{\text{RCH}}$, the battery is present and the IC sets the FAULT bits to 000. If V_{BAT} is below $V_{\text{OREG}}-V_{\text{RCH}}$, the battery is absent and the IC:

- Sets the registers to their default values;
- 2. Sets the FAULT bits to 111; and
- Resumes charging with default values after delay t_{INT}.

Battery Detection During Power-up

At PWRIN POR, if the charger is in 15-Minute Mode (no I^2 C writes from the host detected), the IC starts a 32 ms timer when V_{BAT} crosses V_{SHORT} and starts PWM charging. If V_{BAT} exceeds 3.7 V within a 32 ms period, the IC determines that the battery is not present and:

- 1. Enters Charge Configuration Mode:
- Sets the FAULT bits to 111 (no battery) and resets the SAFETY registers; and
- 3. Disables auto-charging until the next PWRIN POR.

Battery Short-Circuit Protection

If the battery voltage is below the short-circuit threshold (V_{SHORT}); a linear current source, I_{SHORT} , supplies VBAT until $V_{BAT} > V_{SHORT}$.

Charger Status / Fault Status

The STAT pin indicates the operating condition of the IC and provides a fault indicator for interrupt-driven systems. When a fault condition occurs, the STAT pin pulses LOW for 125 μ s. If a new fault replaces the prior fault, STAT issues a new pulse.

The FAULT bits (R0[2:0]) indicate the type of fault in Charge Mode (see Table 14). FAULT bits return to 000 once R0 is read if the fault condition has cleared.

Charge Mode Control Bits

When set, the HZ_VBUS and HZ_VIN bits prevent charging from the VBUS or VIN input sources, respectively. The DIS pin prevents all charging when set, regardless of the state of the HZ bits.

Table 6. DIS Pin and HZ Bit Functionality

Charging	DIS PIN	HZ
ENABLE	0	0
DISABLE	X	1
DISABLE	1	X

Boost Mode

Boost Mode can be enabled when the IC is in 32-Second Mode (host sets TMR_RST before the t_{32SEC} expired) with the OTG pin and OPA_MODE bits as indicated in Table 7. The OTG ACTIVE state is 1 if OTG_PL =1, and 0 when OTG_PL =0.

If boost is active using the OTG pin, boost mode is initiated even if the HZ_VBUS = 1. The HZ_VBUS bit overrides the OPA MODE bit.

Table 7. Enabling Boost

OTG_E N	OTG PIN	HZ_VBU S	OPA_MOD E	BOOS T
1	ACTIVE	X	X	Enabled
1	Х	0	1	Enabled
1	ACTIVE	0	0	Disabled
1	ACTIVE	Х	0	Disabled
0	Х	1	X	Disabled

To remain in Boost Mode, the TMR_RST bit must be set by the host before the t_{32SEC} timer expires. If t_{32SEC} times out in Boost Mode; the IC reverts to High-Impedance Mode, pulses the STAT pin, sets the FAULT bits to 110, and resets the BOOST bit. POR or USB activity clears the fault condition.

The IC can operate its boost regulator while simultaneously charging from VIN. If the IC is charging from VIN when the boost regulator is enabled, charging pauses until the boost soft-start has completed.

Boost PWM Control

The IC uses a minimum on-time, and computed minimum off-time, to regulate V_{BUS} . The computed off-time is designed to keep the switching frequency constant near 3 MHz when the regulator's inductor current is continuous (CCM).

The regulator achieves excellent transient response by employing current-mode modulation. This technique causes the regulator to exhibit a load line. During CCM Mode, the output voltage drops slightly as the input current rises. With a constant V_{BAT} , this appears as a constant output resistance.

The "droop" caused by the output resistance when a load is applied allows the regulator to respond smoothly to load transients with no undershoot from the load line. This can be seen in Figure 34.

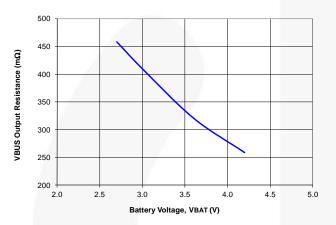


Figure 53. Output Resistance (ROUT)

 V_{BUS} as a function of I_{LOAD} can be computed when the regulator is in PWM Mode (continuous conduction) as:

$$V_{BUS} = 5.05 - R_{OUT} \bullet I_{IOAD}$$
 EQ. 1

At 3.6 V_{BAT} and $I_{LOAD} = 300$ mA, V_{BUS} would droop to about:

$$V_{BLIS} = 5.05 - 0.32 \cdot 0.3 = 4.95V$$
 EQ. 2

At 2.7 V_{BAT} , with $I_{LOAD} = 200$ mA, V_{BUS} would droop to about:

$$V_{BLIS} = 5.05 - 0.45 \cdot 0.2 - 4.96V$$
 EQ. 3

Pulse Frequency Modulated (PFM) Mode

If $V_{BUS} > VREF_{BOOST}$ (nominally 5.05 V) when the minimum off time has ended, the regulator enters PFM Mode. Boost pulses are inhibited until $V_{BUS} < VREF_{BOOST}$. The minimum on-time is increased to enable the output to pump up sufficiently with each PFM boost pulse. The regulator behaves like a constant on-time regulator, with the bottom of its output voltage ripple at 5.05 V in PFM Mode. Since PFM voltage ripple is typically 20 mV_{P-P}, VBUS_(PFM) is nominally 5.06 V.

Table 8. Boost PWM Operating States

State	Description	Invoked When:
SCHK	Short-Circuit Check	$V_{BAT} > V_{BUS}$ and $V_{BUS} < 1V$
LIN1	Linear Startup	V _{BAT} > 1V
SS	Boost Soft-Start	$V_{BUS} < V_{BST}$
BST	Boost Operating Mode	$V_{BAT} > V_{UVLO}$ and SS completed

Shutdown State

When the boost regulator is shut down, Q3 is off, preventing current flow from VBAT to VBUS. Q1 is also off, which prevents current flow from VBUS to VBAT.

SCHK State

The SCHK state turns on a switch with an on-resistance of about 120 Ω from VBAT to VBUS and waits for V_{BUS} to rise to about 1 V before proceeding with boost soft-start. This prevents high current drain from the battery, which could occur if Q3 is turned on into a short circuit. If V_{BUS} fails to rise above 1 V within 8 ms, a boost overload fault is enunciated.

LIN1 State

A portion of Q3 is turned on (on-resistance = 1 Ω) to charge V_{BUS} from 1V to V_{PMID1}. V_{PMID1} is about 0.7 V below V_{BAT}. This state ends when V_{PMID1} - V_{BUS} < 0.4 V. If V_{BUS} fails to achieve V_{PMID1} - 0.4 V within 512 μ s, a boost overload fault is enunciated.

SS State

When $V_{\text{BUS}} > V_{\text{PMID1}} - 0.4 \text{ V}$, the boost regulator begins switching. The output slews up until V_{BUS} is within 10% of its setpoint; at which time, the regulation loop is closed and the boost reference is digitally stepped to 5.07 V.

If the output fails to achieve 90% of its setpoint (V_{BST}) within 512 μs , a boost overload fault is enunciated.

BST State

This is the normal operating mode of the regulator.

Thermal

If the die temperature reaches 120°C while the boost and charger are both operating, charging stops for at least 10 ms, then resumes when the die temperature falls below 120°C.

Boost Fault States

A BOOST fault is enunciated by the STAT pin pulsing and FAULT status bits under any of the following conditions.

Table 9. Fault Status Bits during Boost Mode

Fault Bit		Bit	Foult Description
B2	В1	В0	Fault Description
0	0	0	Normal (no fault)
0	0	1	$V_{BUS} > VBUS_{OVP}$
0	1	0	V _{BUS} fails to achieve the voltage required to advance to the next state during soft-start or sustained (>32 ms) current limit during the BST state.
0	1	1	V _{BAT} < UVLO _{BST}
1	0	0	N/A: This code will not appear
1	0	1	Thermal shutdown
1	1	0	Timer fault
1	1	1	N/A: This code will not appear

Once a fault is triggered, the OPA_MODE bit is reset.

If the boost was started by setting the OTG pin and OTG_EN bits, the boost attempts to restart after a fault following a "cool-off" time of 128 ms.

VREF

The VREF pin provides bias current to the charging circuit while VIN is the power source. This pin follows PMID2, but its voltage is limited to 5.8 V. Up to 5 mA of current can be drawn from the VREF pin to power external devices.

LED Control

An LED driver provides a constant current to drive the anode of a charge indicator LED. The LED flashes during charging. The LED_CONTROL register provides control of the LED driver and can be programmed to flash the LED when charging is disabled.

LED_CONTROL is reset whenever the IC begins charging in 15-Minute Mode. This occurs after VBUS or VIN POR with a weak battery when t_{32SEC} is not running or when t_{32SEC} expires.

Recommended PCB Layout

To limit the high-voltage excursions and stresses on the chargers' internal switching MOSFETs, it is critical to limit the total loop length from PMID back to the GND return, including the length of the CMID bypass capacitors. The layout below achieves this goal.

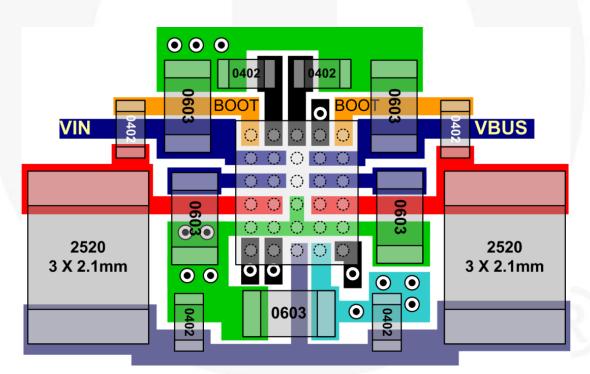


Figure 54. Recommended Layout for High-Current Charging, Using 2520 Inductors

I²C Interface

The serial interface is compatible with Standard, Fast, Fast Plus, and High-Speed Modes per the I²C-Bus® specifications. The SCL line is an input and its SDA line is a bi-directional open-drain output; it can only pull down the bus when active. The SDA line only pulls LOW during data reads and when signaling ACK. All data is shifted in MSB (bit 7) first.

Bus Timing

As shown in Figure 55, data is normally transferred when SCL is LOW. Data is clocked in on the rising edge of SCL. Typically, data transitions shortly at or after the falling edge of SCL to allow ample time for the data to set up before the next SCL rising edge.

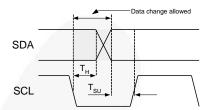


Figure 55. Data Transfer Timing

Each bus transaction begins and ends with SDA and SCL HIGH. A transaction begins with a START condition, which is defined as SDA transitioning from 1 to 0 with SCL HIGH, as shown in Figure 56.

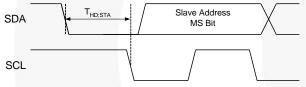


Figure 56. Start Bit

A transaction ends with a STOP condition, which is defined as SDA transitioning from 0 to 1 with SCL HIGH, as shown in Figure 57.

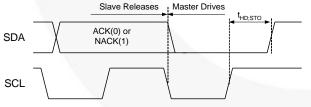


Figure 57. Stop Bit

During a read from the FAN54300 (see Figure 60), the master issues a "REPEATED START" after sending the register address and before resending the slave address. The REPEATED START is a 1-to-0 transition on SDA while SCL is HIGH, as shown in Figure 58.

High-Speed (HS) Mode

The protocols for High-Speed (HS), Low-Speed (LS), and Fast-Speed (FS) Modes are identical, except the bus speed for HS Mode is 3.4 MHz. HS Mode is entered when the bus master sends the HS master code 00001XXX after a START condition. The master code is sent in Fast or Fast-Plus Mode (less than 1 MHz clock). Slaves do not ACK this transmission.

The master then generates a REPEATED START condition (see Figure 58) that causes all slaves on the bus to switch to HS Mode. The master then sends I²C packets, as described above, using the HS Mode clock rate and timing.

The bus remains in HS Mode until a stop bit (Figure 57) is sent by the master. While in HS Mode, packets are separated by REPEATED START conditions (Figure 58).

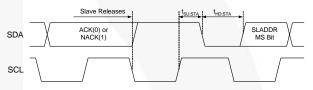


Figure 58. Repeated Start Timing

Read and Write Transactions

The following figures outline the sequences for data read and write. Bus control is signified by the shading of the packet,

defined as Master Drives Bus and Slave Drives Bus All addresses and data are MSB first.

Table 10. Bit Definitions for Figure 59 and Figure 60

Symbol	Definition
S	START, see Figure 56.
Α	ACK. The slave drives SDA to 0 to acknowledge the preceding packet.
Ā	NACK. The slave sends a 1 to NACK the preceding packet.
R	Repeated START, see Figure 58
Р	STOP, see Figure 57.



Figure 59. Write Transaction

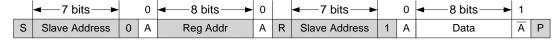


Figure 60. Read Transaction

Register Descriptions

Table 11. I²C Slave Address

	0	1	2	3	4	5	6	7	Hex
VIN Charger	R/W	0	1	0	1	0	1	1	D4
USB Charger	R/W	1	1	0	1	0	1	1	D6

Table 12. I²C Register Address

Name	Register Address	Slave Address	Affects	7	6	5	4	3	2	1	0
CONTROL0_U	0	D6	USB	0	0	0	0	0	0	0	0
CONTROL1_U	1	D6	USB	0	0	0	0	0	0	0	1
OREG_U	2	D6	USB	0	0	0	0	0	0	1	0
IC_INFO_U	3	D6	Both	0	0	0	0	0	0	1	1
IBAT_U	4	D6	USB	0	0	0	0	0	1	0	0
SP_CHARGER_U	5	D6	USB	0	0	0	0	0	1	0	1
SAFE_U	6	D6	USB	0	0	0	0	0	1	1	0
CONTROL0_V	0	D4	VIN	0	0	0	0	0	0	0	0
CONTROL1_V	1	D4	VIN	0	0	0	0	0	0	0	1
OREG_V	2	D4	VIN	0	0	0	0	0	0	1	0
IC_INFO_V	3	D4	Both	0	0	0	0	0	0	1	1
IBAT_V	4	D4	VIN	0	0	0	0	0	1	0	0
SP_CHARGER_V	5	D4	VIN	0	0	0	0	0	1	0	1
SAFE_V	6	D4	VIN	0	0	0	0	0	1	1	0
LED_CONTROL	7	D4/D6	Both	0	0	0	0	0	1	1	1
CHARGE_STATUS	8	D4/D6	Both	0	0	0	0	1	0	0	0
INPUT_STATUS	9	D4/D6	Both	0	0	0	0	1	0	0	1
DIE_REV	14	D4/D6	Both	0	0	0	1	0	1	0	0

Register Bit Definitions

Bit	Name	Туре					Description						
CON	NTROL0_U	I.				Reg Addr: 0	Slave Addr: D6 Default = x	1xx xxxx					
7	TMR_RST	W	Writ	Writing a 1 resets the t _{32SEC} timer. Writing a 0 has no effect.									
′	OTG	R	Retu	urns	the								
6	EN_STU	R/W	0: 1:										
			USE	3 cha	arge	r status							
			Tab	le 1	3. L	JSB Charger Status Bits							
5.4	STAT_U	R		00		Normal (no fault) / Ready							
5:4		ĸ		01		Charge in progress from U							
			10			Charge done							
				11		USB charger fault							
3	BOOST	R	0: 1:										
				Delineates USB Charger and OTG Boost Faults Table 14. USB Fault Bits									
						13D Fault Bits]					
			Bits		0	Charger Mode	Boost Mode	λ,					
			0	0	0	Normal (no fault)	Normal (no fault)						
			0	0	1	V _{BUS} > VBUS _{OVP}	V _{BUS} > VBUS _{OVP}						
2:0	FAULT_U	R	0	1	0	Sleep Mode: V _{BUS} < V _{BAT}	Boost overload						
			0		V _{BAT} < UVLO _{BST}								
			1	0	0	Battery OVP	N/A: This code will not appear						
			1	0	1	Thermal shutdown	Thermal shutdown						
			1	1	0	Timer fault	Timer fault						
			1	1	1	No battery	N/A: This code will not appear						
Note						-							

Note:

7. Default values are in **bold** text.

Bit	Name	Туре	Description							
COI	NTROL1_U		Reg Addr: 1 Slave Addr: D6 Default = 0011 0000							
			USB bus current limit							
			Table 15. IBUSLIM: USB bus current limit							
			[7:6] IBUS Current Limit							
7:6	IBUSLIM	R/W	00 100 mA							
			01 500 mA							
			10 800 mA							
			11 No limit							
			Weak Battery Threshold. This register determines V_{LOWV} threshold when V_{BUS} is charging.							
			Table 16. V _{LOWV} : Weak Battery Threshold							
		- 2	[5:4] IBUS Current Limit							
5:4	VLOWV_U	R/W	00 3.4 V							
			01 3.5 V							
			10 3.6 V							
	//		11 3.7 V							
3	TE_U	R/W	0: Charge termination is disabled when charging from USB.1: Charge termination is enabled for USB charging.							
			0: USB charger is enabled.							
2	CE#_U	R/W	1: USB charger is disabled. This bit is set when $t_{15\text{MIN}}$ expires, regardless of which input source is charging.							
1	HZ_U	R/W	0: USB charger is not in High-Impedance Mode.							
•	112_0	10,00	1: USB charger is in High-Impedance Mode.							
0	OPA_ MODE	R/W	Boost Mode disabled unless enabled with the OTG pin and OTG_EN HIGH. Boost Mode enabled unless HZ U is set.							
OPE	EG_U		1: Boost Mode enabled unless HZ_U is set. Reg Addr: 2 Slave Addr: D6 Default = 0000 1010							
			Charger output "float" voltage when charging from USB source.							
7:2	OREGU	R/W	Programmable from 3.5 to 4.44 V in 20 mV increments. Defaults to 000010 (3.54 V) (see Table 5).							
1	OTG_PL	R/W	0: OTG pin is active LOW.							
'	OIG_IL	17/ 7/	1: OTG pin is active HIGH.							
0	OTG_EN	R/W	OTG pin does not enable boost when HIGH.OTG pin enables boost when HIGH.							
IC_I	INFO_U		Reg Addr: 3 Slave Addr: D4 or D6 Default = 100x x000							
7:5	VENDOR	R	100: Identifies Fairchild as the supplier.							
4:3	PN_U	R	Part number bits. FAN54300 = 10							
2:0	REV	R	IC Revision. Revision is 1.X where X is the decimal of these 3 bits.							
DIE	_REV		Reg Addr: 14H Slave Addr: D4 or D6 Default = 0000 XXXX							
7:4	Reserved	R	These bits return 0.							
3:0	REV_D	R	Die revision. These bits uniquely identify the full revision of the IC. REV bits change whenever there a significant design change. REV_D bits change whenever any masks are revised.							

Bit	Name	Туре							Descr	iption
IBAT	_U			Re	g Addr:	4			Slav	ve Addr: D6 Default = 0000 1001
7	RESETU	W								ave address D4, except the Safety register Read returns 0.
			Sets th	e max	imum ch	arge c	urrent (l	CHARGE)	when o	charging from VBUS when IO_LEVELU = 0.
			Table	17. la	CHARGE A	s a F	unctio	n of th	e ICHG	GU Bits and R _{SENSE} Resistor Value
			BIN	НЕ	V _{RSE}	NSE I	OCHARGE	(mA)		_
			- Diii		(m)	V) (ßmΩ	$100 \text{m}\Omega$	IOREF	
			000	0			550	374	704	
6:4	ICHGU	R/W	001	0			650	442	832	
0.4	icrido	IX/VV	010	0:			750	510	960	
			011	0:			850	578	1088	
			100	0-			950	646	1216	
			101	0:			1,050	714	1344	
			110	0			1,150	782	1472	
			111	0	7 85.	0 /	,250	850	1600	
			Note th	at whe	en chargi	ng fro	m a USI	3 sourc	e, char	ger current is limited to 1250 mA ($R_{SENSE} = 68m\Omega$).
3	Reserved	R	This bit	t returr	ns 1.					
			Sets th	e curre	ent at wh	ich ch	arging to	erminat	es whe	n charging from VBUS if the TE bit is set.
			Table Resist			ermiı	nation	Currer	nt as a	Function of ITERM bits and R _{SENSE}
	- 4		BIN	HEX	V _{RSENSE}	I _{TER}	_и (mA)	Ī		
			DIN	HE >	(mV)		100mΩ	2		
	g1		000	00	3.3	49	33			
2:0	ITERMU	R/W	001	01	6.6	97	66			
			010	02	9.9	146	99			
			011	03	13.2	194	132			
			100	04	16.5	243	165			
			101	05	19.8	291	198			
			110	06	23.1	340	231			
			111	07	26.4	388	264			

Bit	Name	Туре	Description								
SP_	CHARGER_U	J	Reg Addr: 5	Slave Addr: D6 Default = 0x1x x100							
7	Reserved	R	This bit returns 0.								
6	VBUS_CON	R	Mirror of INPUT_STATUS[5] (se	Mirror of INPUT_STATUS[5] (see INPUT_STATUS register description)							
5	IO_LEVEL	R/W	•	by IOCHARGE bits for charging from VBUS. The voltage across R_{SENSE} for output current control is set to 68 m Ω , 221 mA for 100 m Ω).							
4	SPU	R	Special charger loop is not active. Input power source is able to stay above V _{SP} . SPU = 0 when VBUS is not PWM charging. 1: Special charger loop is active and controlling the charging current.								
3	VIN_CON	R	Mirror of INPUT_STATUS[7] (see INPUT_STATUS register description)								

Bit	Name	Туре						Description
			Sets the s	special s voltag	charger o	control lo y current	op refer is reduc	ence voltage when charging from V_{BUS} . If V_{BUS} falls sed until the input voltage is at or above V_{SP} .
			Table 19). V _{SP} (Special	Charge	r Refer	ence Voltage
			DEC	BIN	V _{SP}	J		5
			0	000	4.21			
2:0	VSPU	R/W	1	001	4.29			
2.0	VO. 0	10,00	2	010	4.37			
			3	011	4.45			
			4	100	4.53			
			5	101	4.61			
			6	110 111	4.69 4.77			
								01 11 50 5 6 11 0100 0000
-	E_U			g Addı				Slave Addr: D6 Default = 0100 0000
7	Reserved	R	This bit re					
	- 4		Any attem ISAFEU.	npt to w	rite a val	ue to ICI	HGU hig	her than the contents of ISAFEU sets ICHGU =
			Table 20). USB	Chargi	ng I _{CHAF}	RGE Lim	it as a Function of the ISAFEU Bits
			BIN	HEX	V _{RSENSE}		(mA)	
			000	00	(mV)	68mΩ 550	100mΩ 374	-
6:4	ISAFEU	R/W	000	00 01	37.4 44.2	650	442	
			010	02	51.0	750	510	
	Ď.		011	03	57.8	850	578	
			100	04	64.6	950	646	
			101	05 06	71.4 78.2	1,050 1,150	714 782	-
			111	07	85.0	1,150	850	1
			Any attem (below) re					at is higher than the value in the Max. OREG column
			, ,					of the VSAFEU Bits when Charging from
			VBUS					_
			DEC	BIN	Max O	_	VOREG	A
	$\langle \cdot \rangle$		0	0000	(REG2		MAX 4.20	
			1	0001	1001		4.22	
			2	0010	1001	01	4.24	
			3	0011	1001	10	4.26	
3:0	VSAFEU	R/W	4	0100	1001		4.28	
			5	0101	1010		4.30	
	1		7	0110	1010		4.32	
			8	0111 1000	1010		4.34 4.36	
			9	1000	1010		4.38	
				1010	1011		4.40	
			10				4.42	
			10 11	1011	1011	.10	4.42	
			11 12	1011 1100	1011 1011		4.44	
			11 12 13	1011 1100 1101		.11	4.44 4.44	
			11 12	1011 1100	1011	11 000 001	4.44	

		ı							
Bit	Name	Type	Description						
CON	NTROL0_V	ı	Reg Addr: 0 Slave Addr: D4 Default = x1xx 0xxx						
	TMR_RST	W	Writing a 1 resets the t _{32SEC} timer. Writing a 0 has no effect.						
	SRST	R	Returns the SRST pin level (1 = SRST pin HIGH).						
6	EN_STV	R/W	 STAT pin does not go LOW when charging from V_{IN} source. STAT pin function is enabled for V_{IN} source. 						
			Table 22. VIN Charger Status Bits						
E. 1	CTAT V	ь	00 Normal (no fault)						
5:4	STAT_V	R	01 Charge in progress from VIN source						
			10 Charge Done						
			11 VIN charger fault						
3	Reserved	R	This bit returns 0.						
			Delineates VIN Charger Faults						
			Table 23. VIN Charger Fault Bits						
	- 4		Bits Charger Mode						
			2 1 0 Charger Mode						
			0 0 0 Normal (no fault)						
2:0	FAULT_V	R	0 0 1 V _{IN} > VIN _{OVP}						
2.0	17.021_	'`	0 1 0 Sleep Mode: V _{IN} < V _{BAT}						
			0 1 1 Poor VIN input source						
			1 0 0 Battery OVP						
			1 0 1 Thermal shutdown						
			1 1 0 Timer fault						
			1 1 1 No battery						
CON	NTROL1_V		Reg Addr: 1 Slave Addr: D4 Default = 0111 0000						
7:6	Reserved	R/W	These bits have no effect on IC operation. Input current is not limited by the IC when charging from VIN.						
5:4	VLOWV_V	R/W	See Table 16. VLOWV: Weak Battery Threshold						
3	TE_V	R/W	0: Charge termination is disabled when charging from VIN.						
			1: Charge termination is enabled for VIN charging.						
2	CE#_V	R/W	 VIN charger is enabled. 1: VIN charger is disabled. This bit is set when t_{15MIN} expires, regardless of which input source is 						
_	OL#_V	10,44	charging.						
1	U7 \/	R/W	0: VIN charger is not in High-Impedance Mode.						
1	HZ_V	K/VV	1: VIN charger is in High-Impedance Mode.						
0	Reserved	R	This bit returns 0.						
ORE	G_V	1	Reg Addr: 2 Slave Addr: D4 Default = 0000 1010						
7:2	OREGV	R/W	Charger output "float" voltage when charging from VIN source. Programmable from 3.5 to 4.44 V in 20 mV increments. Defaults to 000010 (3.54 V) (see Table 5).						
1:0	Reserved	R	These bits return 10.						
IC_I	NFO_V	,	Reg Addr: 3 Slave Addr: D4 Default = 100x x000						
7:5	VENDOR	R	100: Identifies Fairchild as the supplier.						
4:3	PN_V	R	Part number bits: FAN54300 = 00						
2:0	REV	R	IC Revision: Revision is 1.X, where X is the decimal of these 3 bits.						

Bit	Name	Туре						ļ	Des	scription	
IBA	T_V		•	R	eg Add	lr: 4				Slave Addr: D4 Default = 0000 0001	
7	RESETV	W								slave address D4, except the Safety register (Registerns 0.	j6),
			Sets the	maxin	num ch	arge c	urrent (I	CHARGE) W	hen	n charging from VIN when IO_LEVELV = 0.	
			Table 24	4. I _{CHA}	RGE Cu	rrent a	as a Fur	ction of	the	e ICHGV Bits and R _{SENSE} Resistor Value	
			BIN	HEX	V _{RSE}		OCHARGE 68mΩ	(mA)			
			0000	00	37.		550	374			
			0001	01	44.		650	442			
			0010	02	51.		750	510			
6:3	ICHGV	R/W	0011	03	57.		850	578			
0.5	101101	1 1 / V V	0100	04	64.		950	646			
			0101	05	71.	4 1	1,050	714			
		- 4	0110	06	78.	2 1	1,150	782			
		- 40	0111	07	85.	0 1	1,250	850			
		./*	1000	08	91.	8 1	1,350	918			
			1001	09	98.	6 1	1,450	986			
			1010	0A	105	.4 1	1,550	1,054			
			Any atte	mpt to	write a	value l	higher th	an 1010	resu	ults in ICHGV = 1010.	
			Table 2	25. I _{CH}	ARGE TO					the TE bit is set: a Function of the ITERM bits and R _{SENSE}	
			Resisto	or Val	ue						
			BIN I	768	RSENSE (mV)		(mA) 100mΩ	}			
			000	00	3.3	49	33				
2:0	ITERMV	R/W	001	01	6.6	97	66				
			010	02	9.9	146	99				
					13.2	194	132				
					16.5	243	165				
			101	05	19.8	291	198				
			110	06	23.1	340	231				
			111	07	26.4	388	264				

Bit	Name	Туре		Description					
SP_	CHARGER_V		Slave Addr: D4 Default = 0x1x x100						
7	Reserved	R	This bit returns 0.						
6	VIN_CON	R	Mirror of INPUT_STATUS[7] (see	INPUT_STATUS register description)					
5	IO_LEVELV	R/W	•	y IOCHARGE bits for charging from VIN. ge across R_{SENSE} for output current control is set to 22.1mV A for 100m Ω).					
4	SPV	R	charging.	V_{IN} is able to stay above V_{SP} . SPV = 0 when VIN is not PWM and controlling the charging current.					
3	EN_LEVEL	R	0: DISABLE (DIS) pin is LOW. 1: DISABLE (DIS) pin is HIGH						
2:0	VSPV	R/W	Sets the special charger control loop reference voltage when charging from VIN. If V _{iv.} falls help						

Bit	Name	Туре	Description							
SAFE	_ V	•	F	Reg Ad	dr: 6			Slave Addr: D4 Default = 0100 0000		
			Any atter	npt to w	vrite a val	ue highe	than 10	er than the contents of ISAFEV sets ICHGV = ISAFEV. 10 to ISAFEV results in ISAFEV = 1010. of the ISAFEV Bits when Charging from VIN		
			BIN	HEX	V _{RSENSE}	I _{SAFE}	(mA)			
			DIN	I ILX	(mV)	68mΩ	$100 \text{m}\Omega$			
			0000	00	37.4	550	374			
			0001	01	44.2	650	442			
7:4	ISAFEV	R/W	0010	02	51.0	750	510			
			0011	03	57.8	850	578			
			0100	04	64.6	950	646			
			0101	05	71.4	1,050	714			
			0110	06	78.2	1,150	782			
			0111	07	85.0	1,250	850			
			1000	08	91.8	1,350	918			
			1001	09	98.6	1,450	986			
			1010	0A	105.4	1,550	1,054			
3:0	VSAFEV	R/W						t is higher than the value in the Max OREG column e Table 21).		

Bit	Name	Туре		Description						
LED	_CONTROL	•	Reg Addr: 7	Slave Addr: D4 or D6						
		y	Sets LED behavior							
			Table 27. LED Control Bits	s						
7:6	I_LED	R/W	00 LED is off							
7.0	1_555	10,00	01 LED current = 1.13 mA							
			10 LED current = 2.25mA							
			11 LED current = 4.50 mA							
5	Reserved	R	This bit returns 0.							
4	LED_ON	R/W	LED is only active when charging. LED is active regardless of charging status.							
			Sets LED blink toN							
			Table 28. LED ON-Time							
3:2	LED_TON	R/W	00 131 ms							
3.2	LED_TON	IN/VV	01 262 ms							
			10 524 ms							
			11 Constant ON							
			Sets LED blink t _{OFF}							
			Table 29. LED OFF-Time							
1:0	LED_TOFF	R/W	00 393 ms							
1.0	LLD_1011	17/77	01 786 ms							
		10 1573 ms								
			11 3146 ms							

Bit	Name	Туре	Description
	ARGE STATUS		Reg Addr: 8 Slave Addr: D4 or D6
7	ITERM_CMP	R	0: If TE = 1, $(V_{CSIN} - V_{BAT}) < V_{ITERM}$. If TE = 0, $(V_{CSIN} - V_{BAT}) < 1 \text{ mV}$. 1: If TE = 0, $(V_{CSIN} - V_{BAT}) > V_{ITERM}$. If TE = 0, $(V_{CSIN} - V_{BAT}) > 1 \text{ mV}$.
6	T_120	R	0: The die temperature is below 120°C.1: The die temperature is above 120°C.
5	ICHG	R	10: ICHARGE loop is controlling charge current (charger is in CC Mode).11: ICHARGE loop is not controlling charge current.
4	IBUS	R	 0: IBUS is limiting charge current. 1: IBUS loop is not controlling charge current. This bit always = 1 when charging from VIN.
3	CV	R	1 indicates that the constant-voltage loop (OREG) is controlling the charger and that all current limiting loops have released. Deglitched 32ms.
2	LINCHG	R	 0: Charger is not in Linear Mode 1: Charger is in Linear Mode (V_{BAT} < V_{SHORT}).
1:0	Reserved	R	These bits always return 0.
INP	UT_STATUS		Reg Addr: 9 Slave Addr: D4 or D6
7	VIN_CON	R	 0: V_{IN} has been less than V_{BAT} for at least 100ms (VIN is disconnected). 1: V_{IN} > V_{BAT} and V_{IN} > 4.5 V for at least 4ms (VIN is connected). This bit is mirrored in SP_CHARGER_U[3] and SP_CHARGER_V[6].
6	VIN_VALID	R	 0: V_{IN} has not passed validation. 1: V_{IN} has passed validation and can be used as a charging source.
5	VBUS_CON	R	 V_{BUS} has been less than V_{BAT} for at least 100ms (VBUS is disconnected). V_{BUS} > V_{BAT} and V_{BUS} > 4.5 V for at least 4ms (VBUS is connected).
4	VBUS_VALID	R	 0: V_{BUS} has not passed validation. 1: V_{BUS} has passed validation and can be used as a charging source. This bit is mirrored in SP_CHARGER_U[6].
3	SOURCE	R	 0: V_{IN} is used for IC power and charging. 1: V_{BUS} is used for IC power and charging.
2:0	Reserved	R	These bits always return 0.

Physical Dimensions

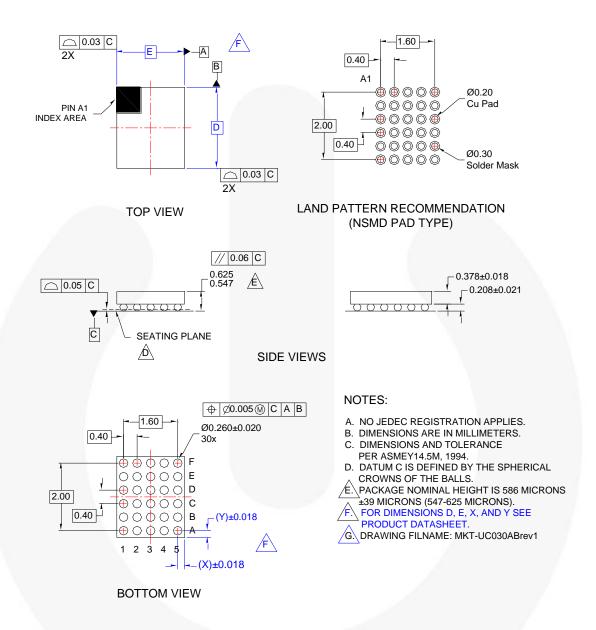


Figure 61. 30-Ball, WLCSP, 5x6 Array, 0.4 mm Pitch, 586 µm Package Height

Product-Specific Dimensions

Product	D	E	X	Y
FAN54300UCX	2.460 ±0.030 mm	2.26 ±0.030 mm	0.330 mm	0.230 mm

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